

2022 IEEE International Symposium on Radio-Frequency Integration Technology, 8/30/2022, Busan, Korean

100-300GHz MIMO Communications: Transistors, ICs, Arrays, and Systems



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Acknowledgement: This work was supported in part by the Semiconductor Research Corporation (SRC) and DARPA.

Acknowledgements

Systems

Sundeeep Rangan
Networks, Applications, MIMO, Power

Upamanyu Madhow
MIMO algorithms
Imaging algorithms
Compressive imaging
UC Santa Barbara

Christoph Studer
MIMO algorithms
VLSI MIMO
digital beamforming
Cornell

Andreas Molisch
100-300GHz
propagation
measurements
USC

Danijela Cabric
MIMO
algorithms
(funding via CONIX)
UCLA

ICs

Ali Niknejad
mm-wave CMOS: hub
mm-wave arrays
mm-wave MIMO
UC Berkeley

James Buckwalter
efficient PAs
III-V arrays
UC Santa Barbara

Kenneth O
140-300GHz
SiGe ICs
UT Dallas

Muhannad Bakir
high-frequency
packaging
Georgia Tech

Gabriel Rebeiz
mm-wave CMOS: handset
mm-wave arrays
UC San Diego

Alyosha Molnar
N-path mixers
MIMO ADCs
Cornell

Elad Alon
design automation
equalizers
UC Berkeley

Tim Fisher
advanced
packaging
materials
UCLA

Andrew Kummel
advanced
packaging
materials
UCSD

Transistors

Umesh Mishra
N-polar GaN HEMTs
for 140, 210GHz
UC Santa Barbara

Huili (Grace) Xing
AlN/GaN HEMTs
for 140, 210GHz
Cornell

Susanne Stemmer
transistors in
novel materials
UC Santa Barbara

Debdeep Jena
GaN HEMTs
on Si
Cornell

Srabanti Chowdhury
Diamond cooling
for GaN
UC Davis

Massive MIMO demo.

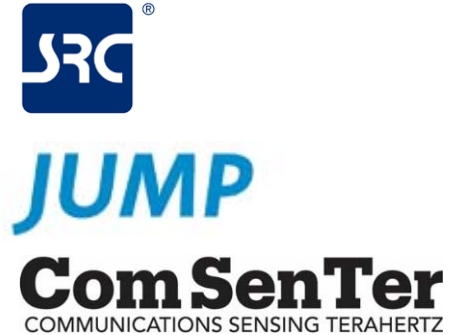
Borivoje Nikolic
VLSI design automation
VLSI MIMO processors
UC Berkeley

Compressive imaging

Amin Arbabian
140GHz radar chipsets
and arrays
Stanford

140/210/280GHz arrays
for demos.

Mark Rodwell
THz HBTs for PAs
THz HEMTs for LNAs
UC Santa Barbara



Also:

[Kyocera](#): D. Kim, H. Horikawa, M. Imayoshi.

[Samsung](#): G. Xu, N. Sharma, S. Abu-Surra, W. Choi

[Pi-Radio](#): A. Dhananjay,



100-300GHz Wireless

Wireless networks: exploding demand.

Immediate industry response: 5G.

~3~100 GHz

increased spectrum, extensive beamforming

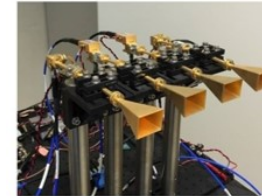
Next generation (6G ??): above 100GHz.. (???)

greatly increased spectrum, massive spatial multiplexing

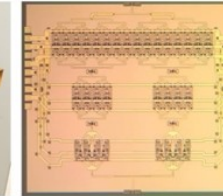
— Services —



— Systems —



— ICs —

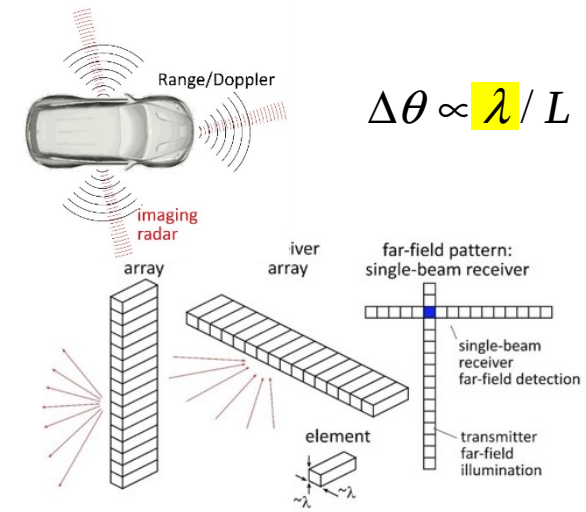
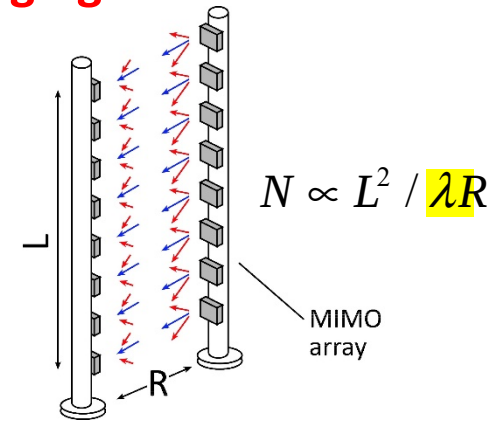
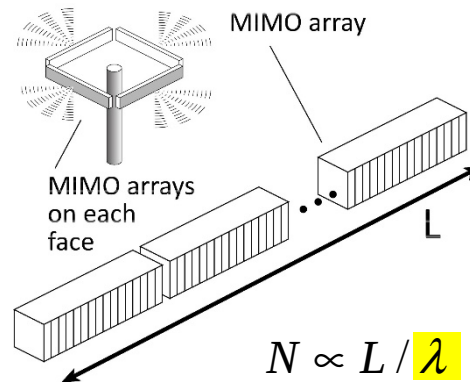
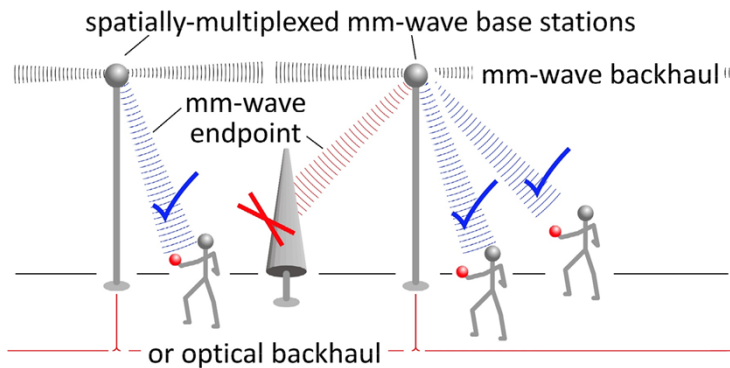


— Devices —



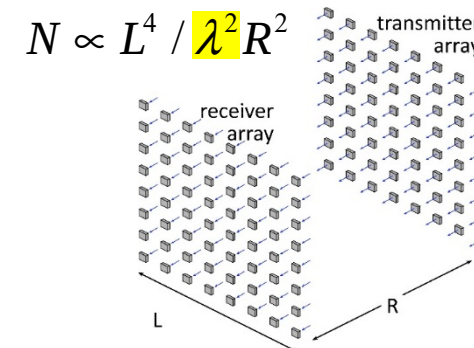
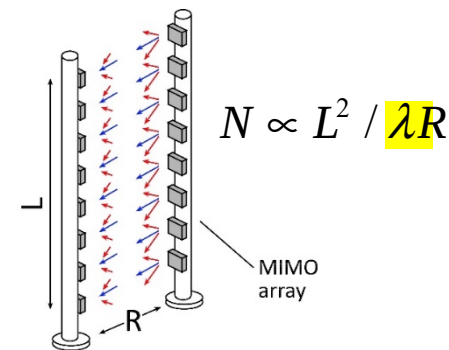
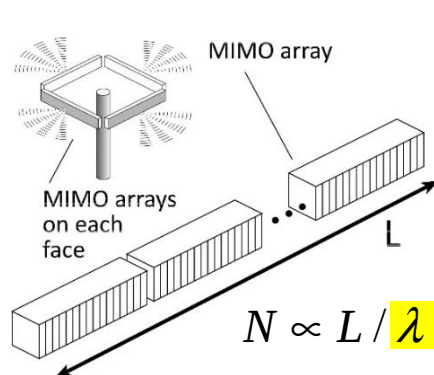
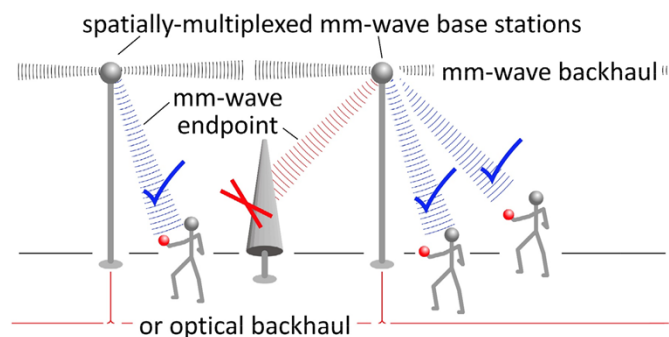
100-300GHz carriers, massive spatial multiplexing

→ Terabit hubs and backhaul links, high-resolution imaging radar

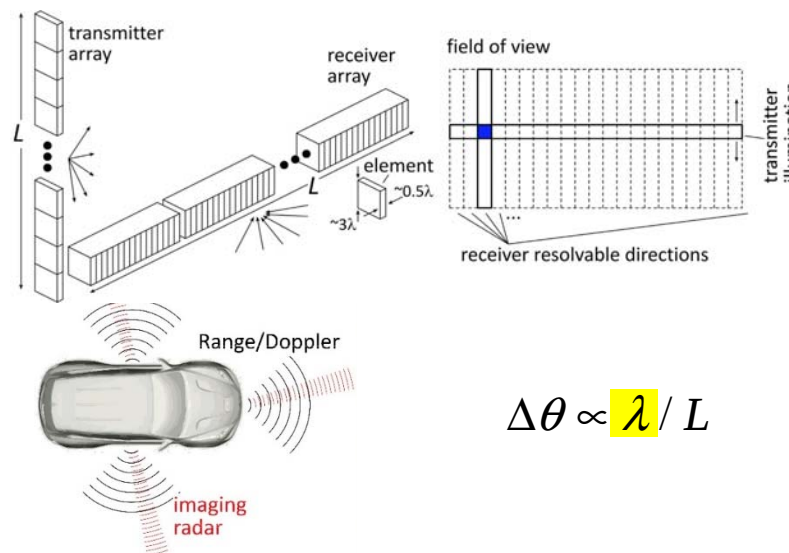


Benefits of Short Wavelengths

Communications: Massive spatial multiplexing, massive # of parallel channels. **Also, more spectrum.**



Imaging: very fine angular resolution

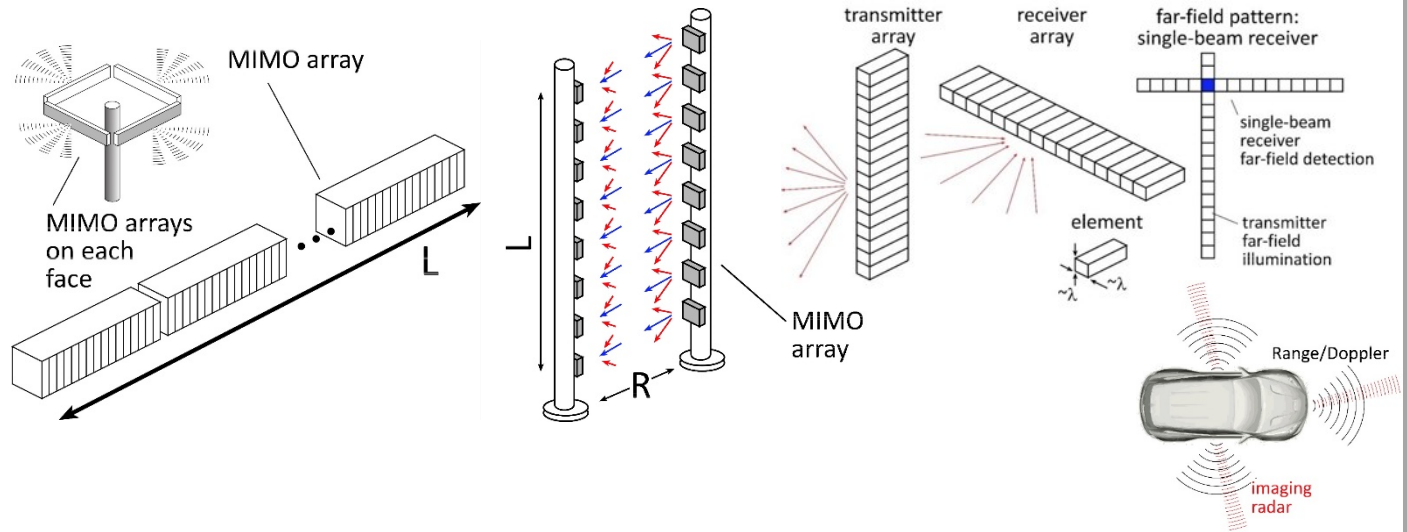
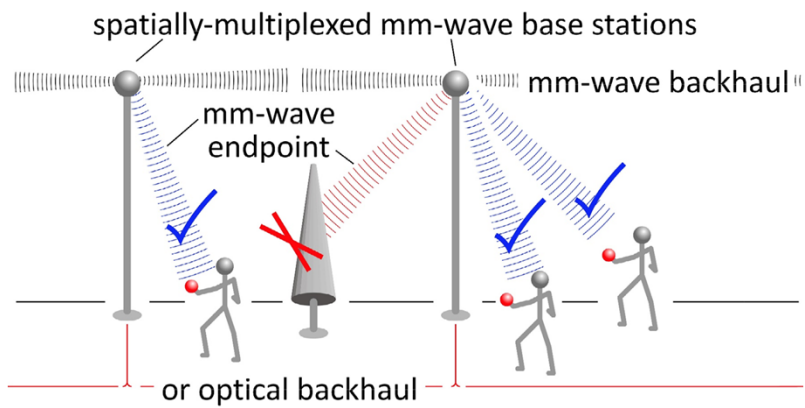


But:

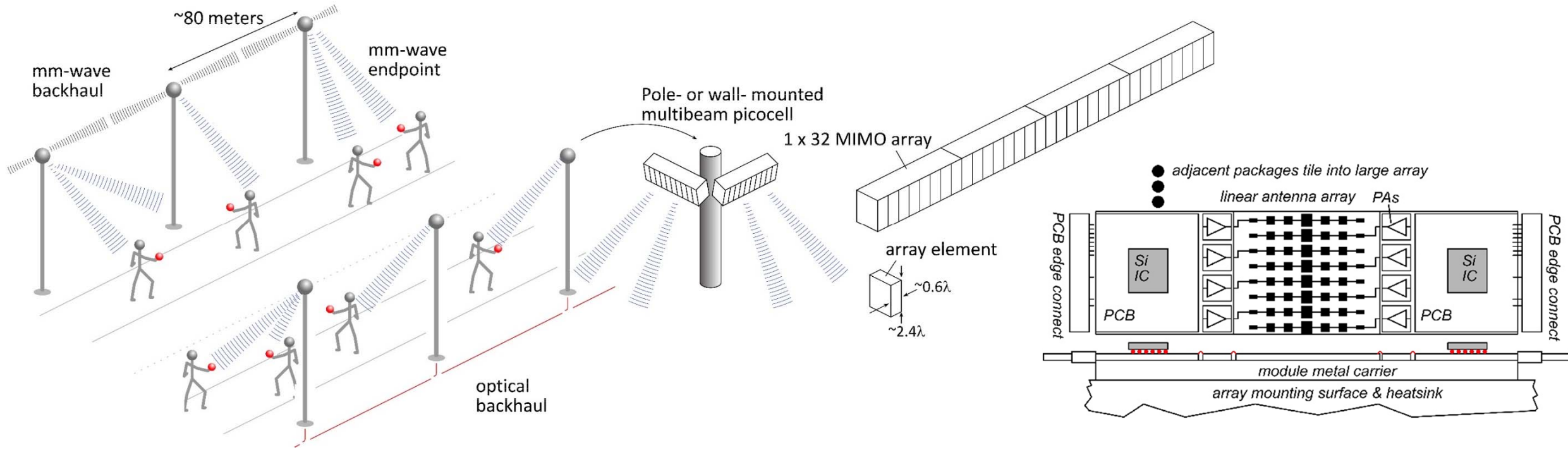
High losses in foul or humid weather.
High λ^2/R^2 path losses.
ICs: poorer PAs & LNAs.
Beams easily blocked.

100-300GHz wireless:
terabit capacity,
short range,
highly intermittent

Applications



140GHz moderate-MIMO hub

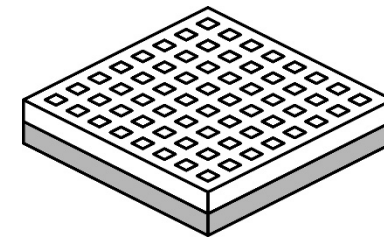


If demo uses 32-element array (four 1×8 modules):

16 users/array. $P_{1dB} = 21 \text{ dB}_m$ PAs, $F = 8 \text{ dB}$ LNAs

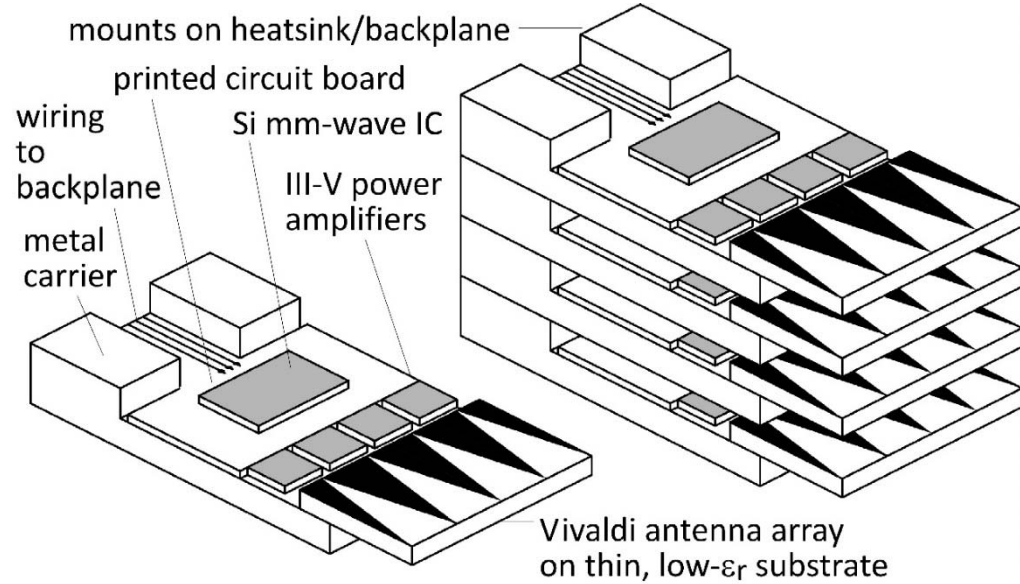
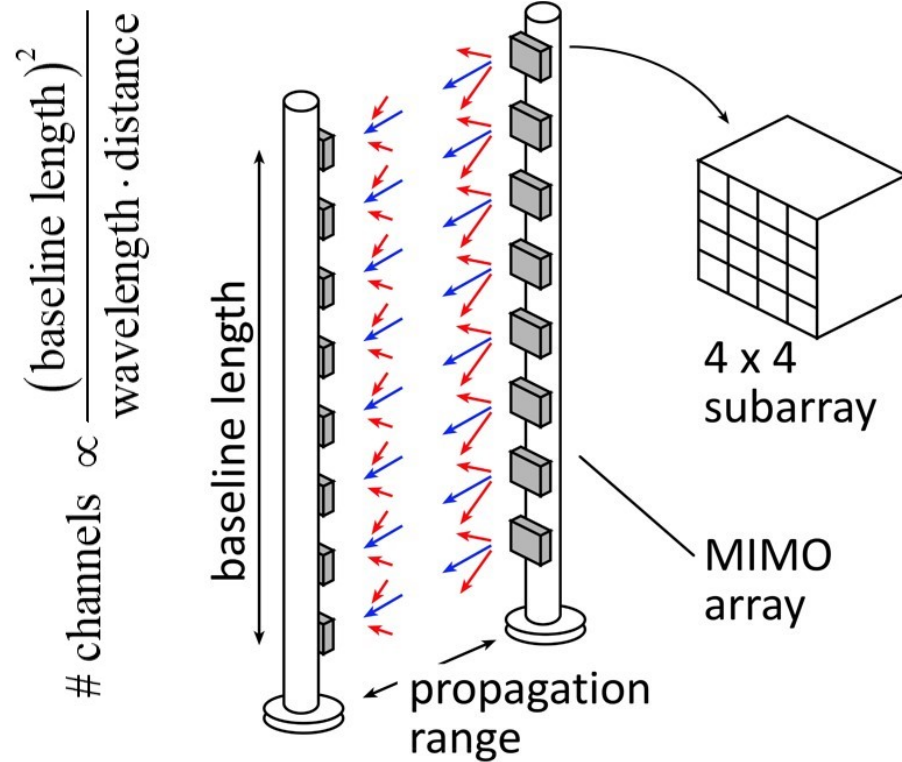
1, 10 Gb/s/beam → 16, 160 Gb/s total capacity

70, 40 m range in 50mm/hr rain with 17dB total margins



Handset:
8 × 8 array
(9×9mm)

210 GHz, 640 Gb/s MIMO Backhaul



8-element MIMO array

2.1 m baseline.

80Gb/s/subarray → 640Gb/s total

4 × 4 sub-arrays → 8 degree beamsteering

Key link parameters

500 meters range in 50 mm/hr rain; 23 dB/km

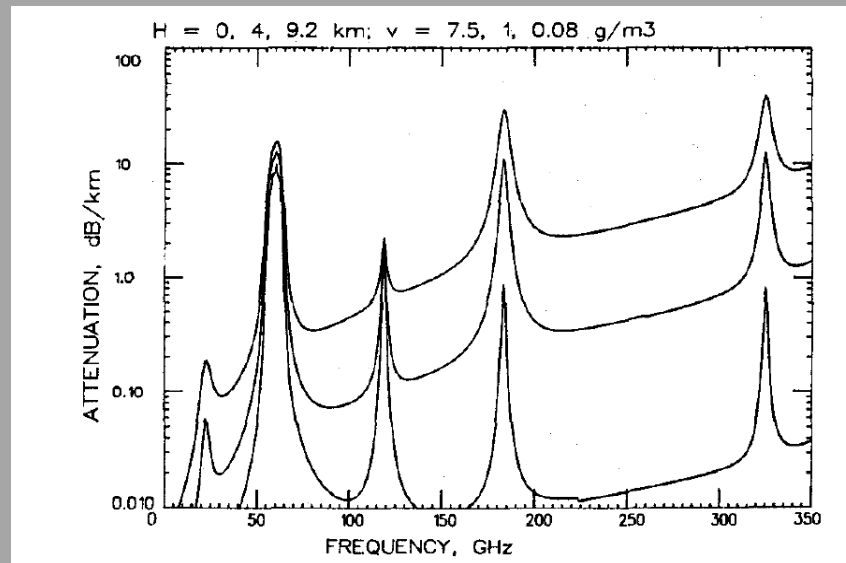
20 dB total margins:

packaging loss, obstruction, operating,
design, aging

PAs: 18dBm = $P_{1\text{dB}}$ (per element)

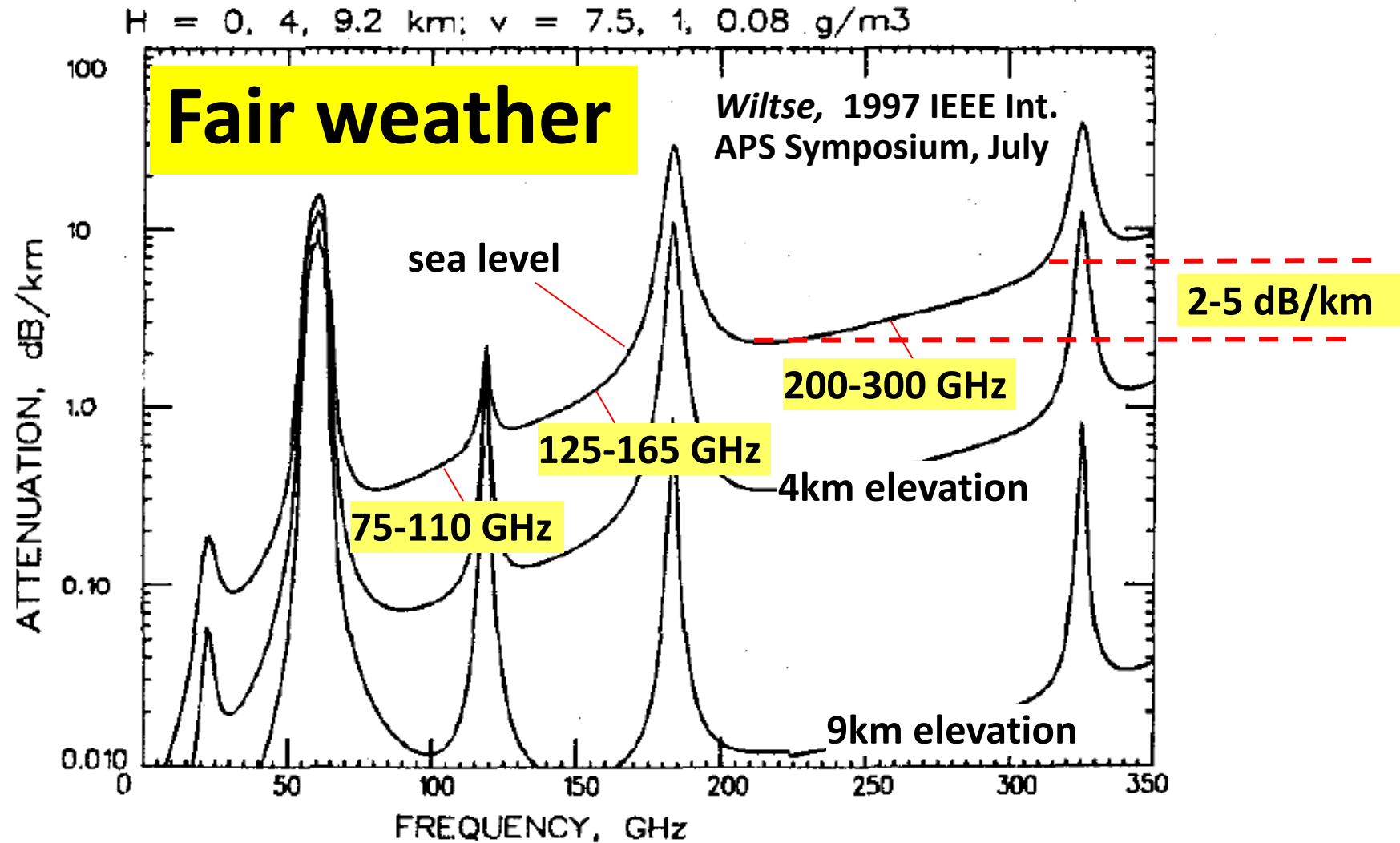
LNAs: 6dB noise figure

mm-wave propagation



?

Fair-Weather Propagation



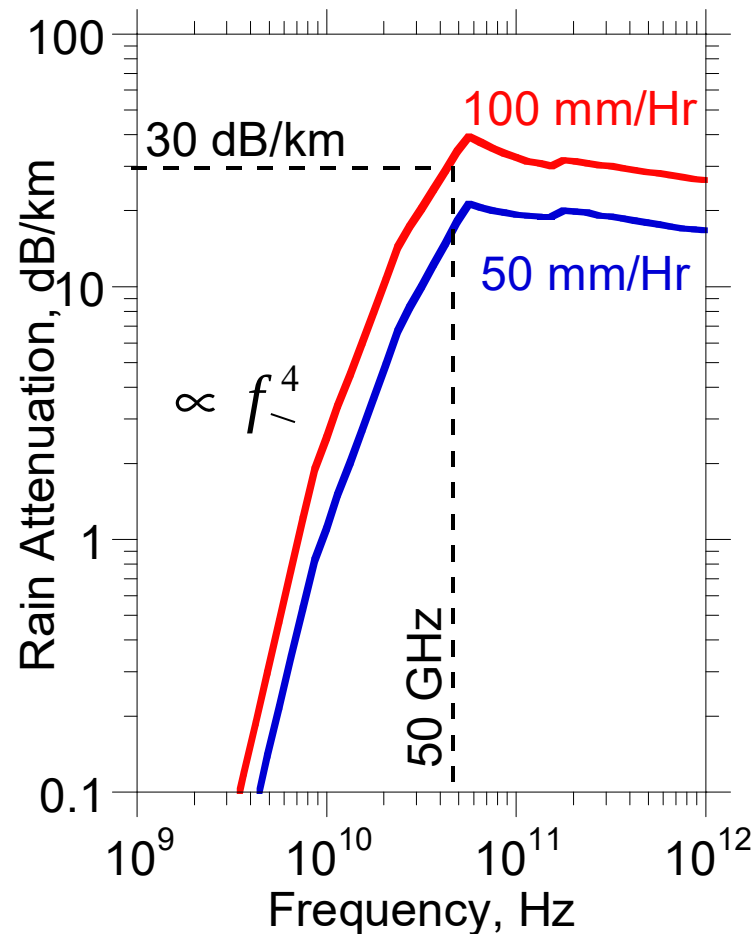
**Caution: wireless services must work reliably, not only in best-case conditions.
Must consider worst-case (10^{-4} , 10^{-5} probability) atmospheric attenuation**

Systems must work in most weather

Rain:

10^{-4} : 50-85mm/hr, 19dB/km

10^{-5} : 100+mm/hr: 30dB/km



35°C, 90% Humidity

300GHz: 30 dB/km

400GHz: 100 dB/km

450GHz: 200 dB/km

650GHz: 300 dB/km

850GHz: 300 dB/km

1000GHz: 1000 dB/km

Appleby, Wallace, IEEE Trans Ant & Prop, Nov. 2007

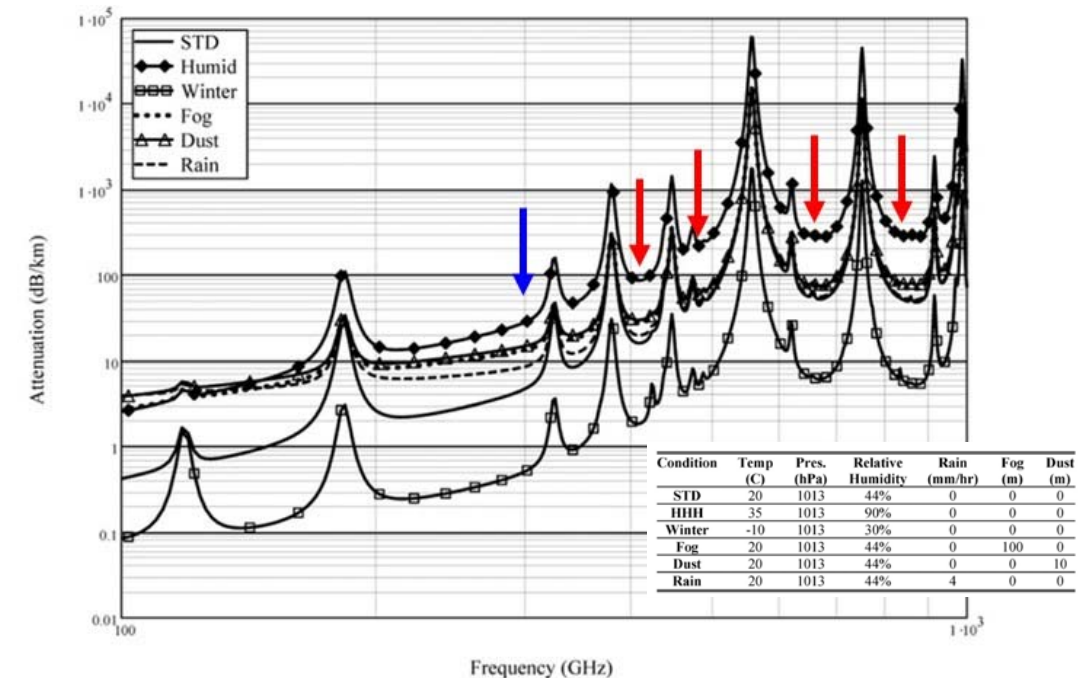
Rosker; Wallace, 2007 IEEE IMS

Olsen, Rogers, Hodge, IEEE Trans Antennas & Propagation Mar 1978

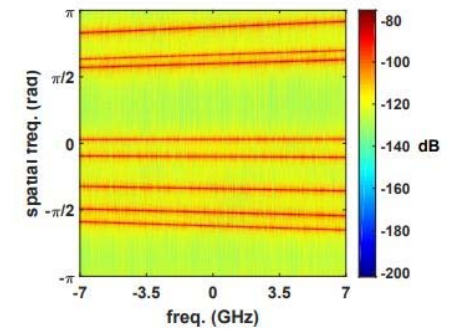
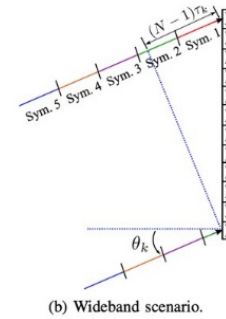
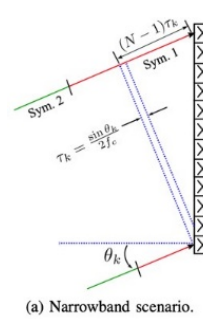
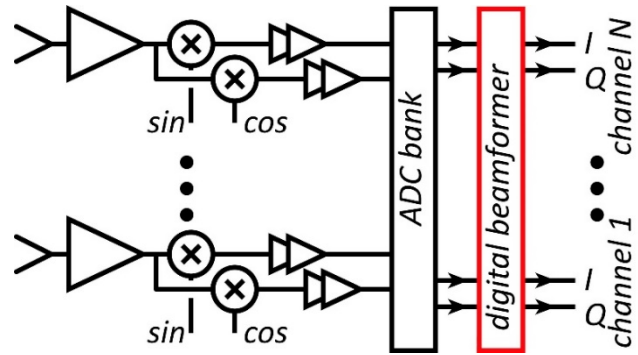
Liebe, Manabe, Hufford, IEEE Trans Antennas and Propagation, Dec. 1989

Liebe, IEEE Trans Ant and Pro, Vol 31, No. 1, Jan 1983

Karasawa, Maekawa, IEEE Proc, Vol 85, #6, June 1997



Systems



MIMO System Design

M antennas, K signals: **spatial oversampling**.

ADCs/DACs¹: effective # bits increased by $\log_4(M/K)$

Given QPSK, 2:1 spatial oversampling, only need 3-4 bits

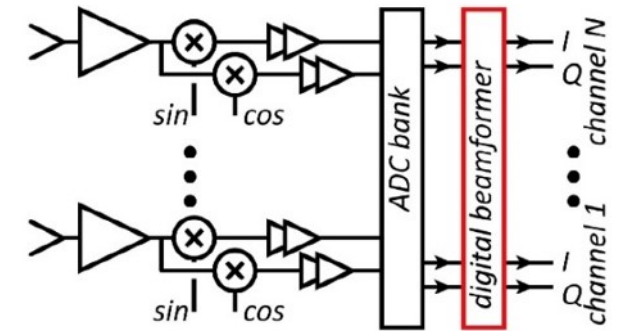
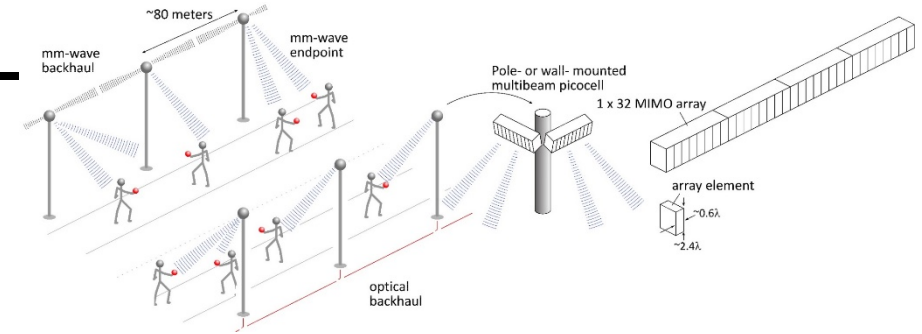
Linearity¹: Amplifier P_{1dB} need be only 4 dB above average power

Phase noise^{2,3}: Requirements similar to SISO

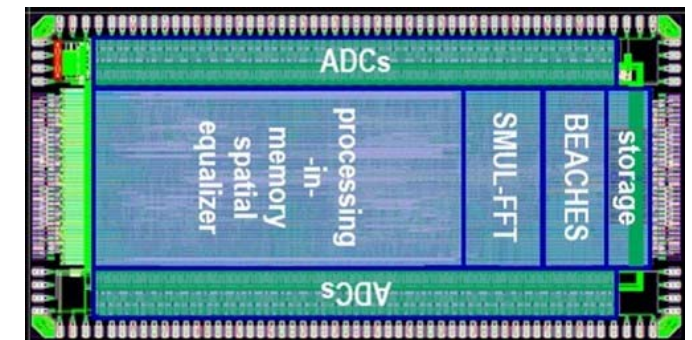
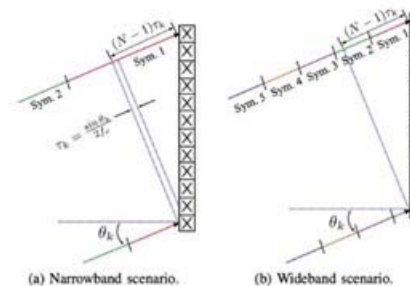
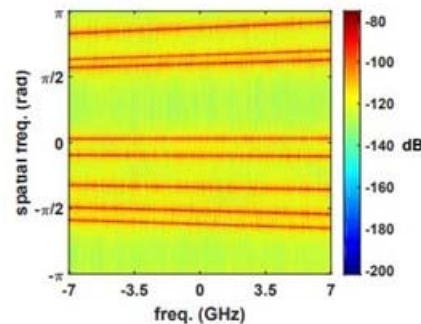
Efficient digital beamforming^{4,5}: beamspace algorithm

Efficient VLSI digital beamformer implementation⁶: low-resolution matrix

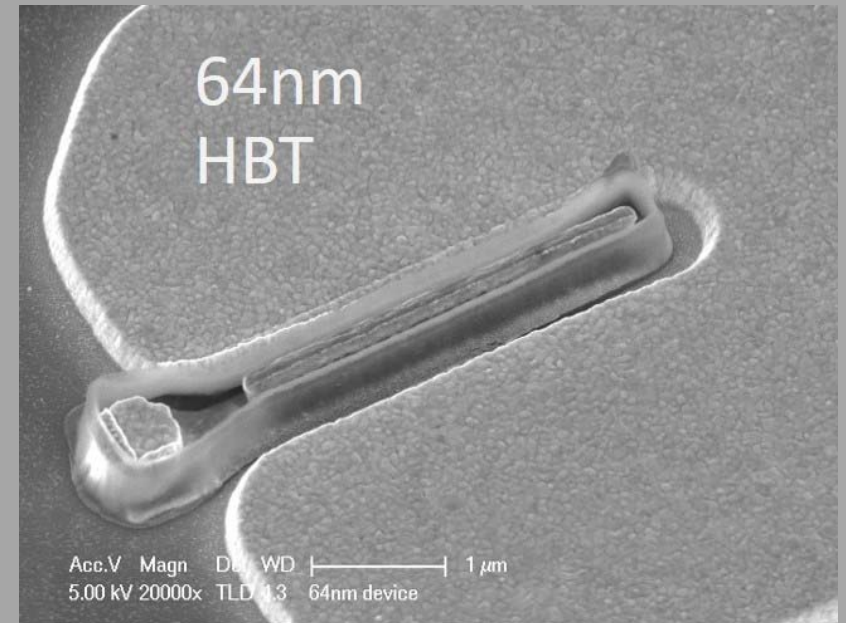
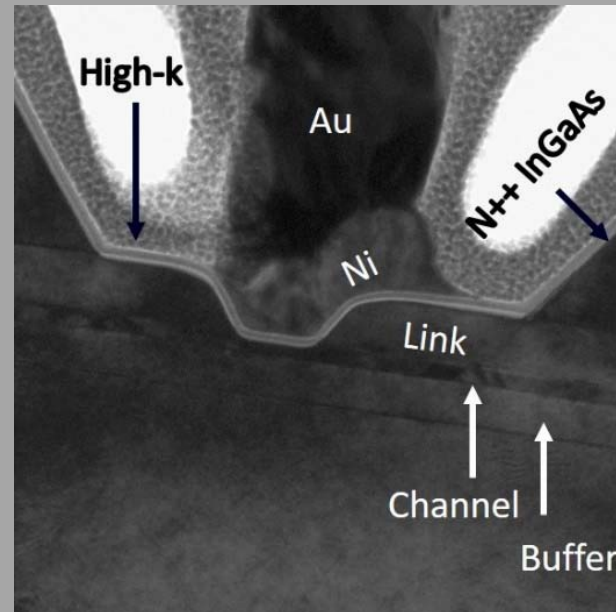
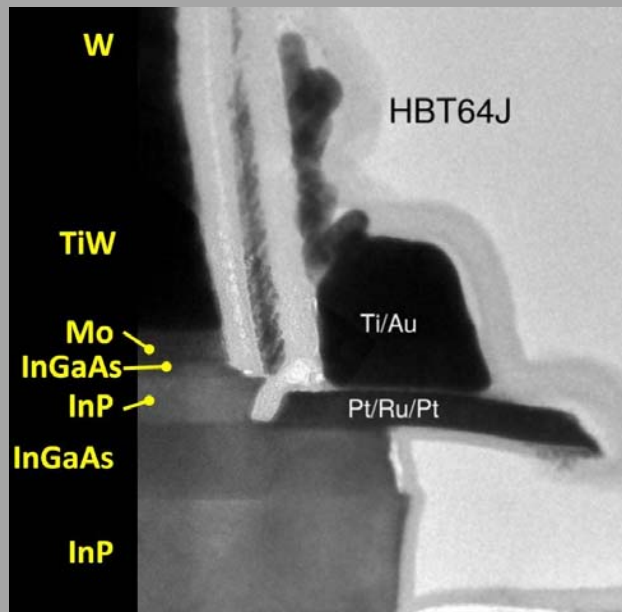
Efficient beamforming in broadband arrays⁷: combined spatial & temporal FFTs.



- 1) M. Abdelghany et al, IEEE Trans. Wireless Comm, Sept. 2021
- 2) M. E. Rasekh et al, IEEE Trans. Wireless Comm, Oct. 2021
- 3) A. Puglielli et al, 2016 IEEE ICC
- 4) M. Abdelghany, et. al, , 2019 IEEE SPAWC
- 5) S. H. Mirfarshbafan et al, IEEE Trans CAS 1, 2020
- 6) O Castañeda Fernández et. al, 2021 ESSCIRC
- 7) M. Abdelghany et al 2019 IEEE GLOBECOM



Transistors



Transistors for 100-300GHz

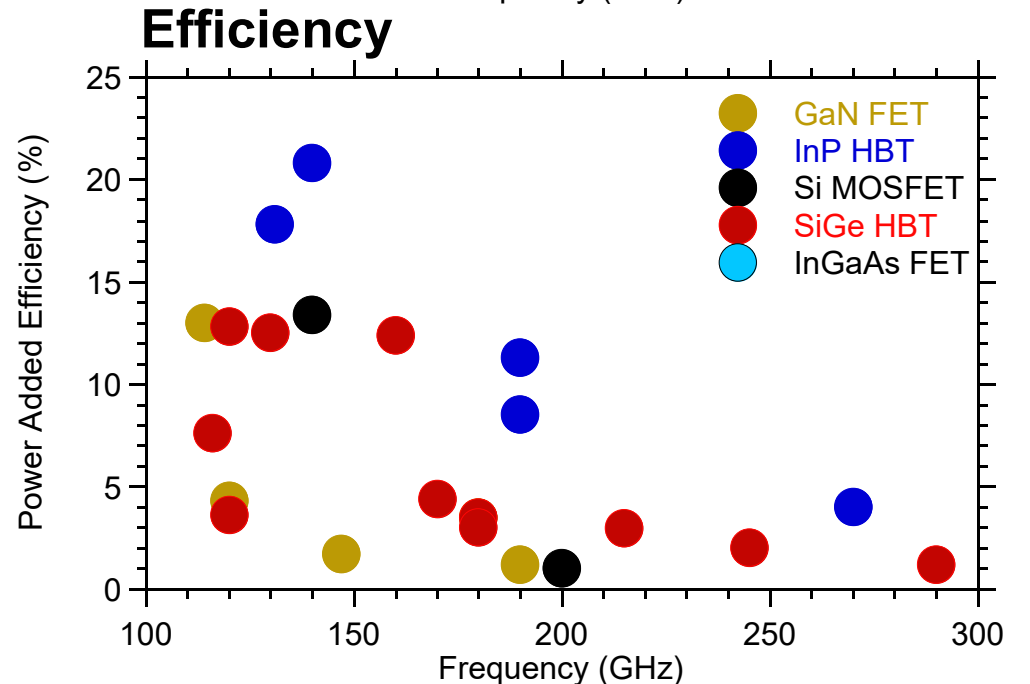
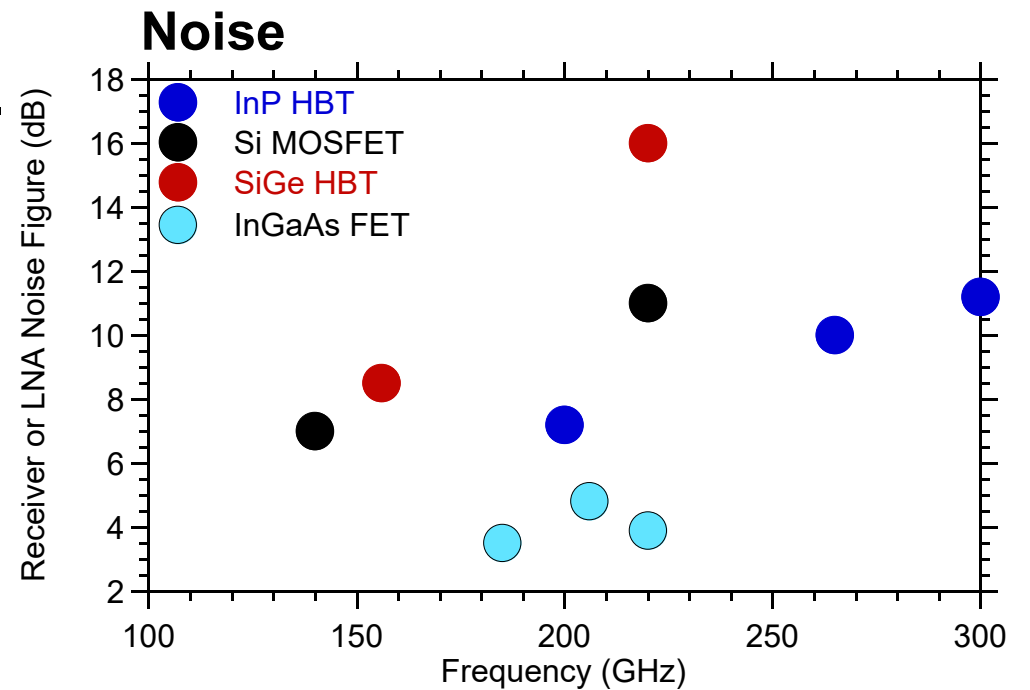
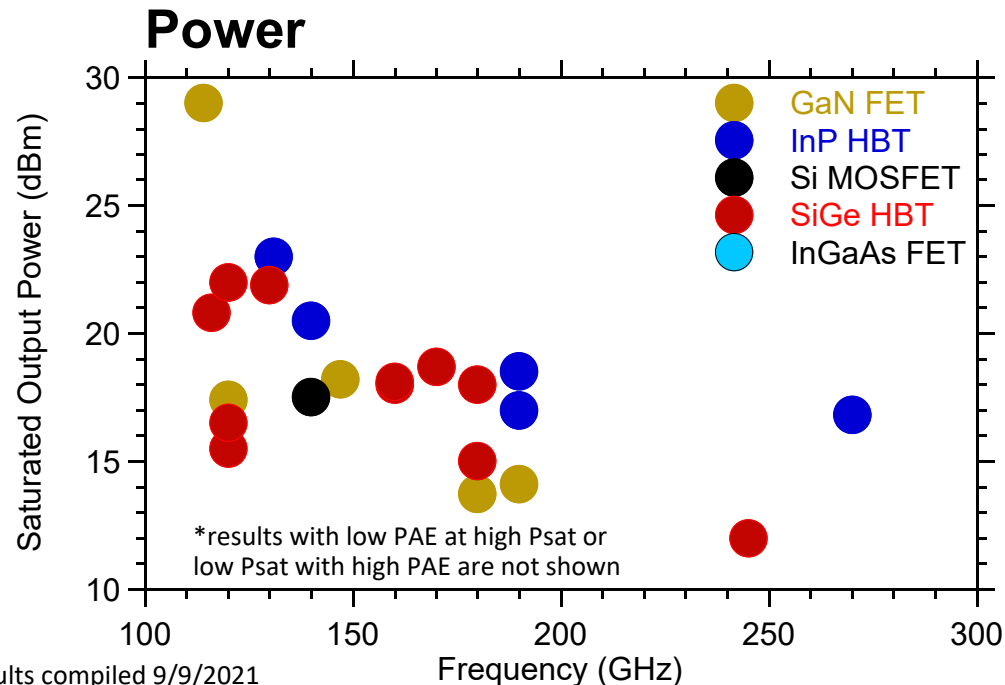
CMOS: good power & noise up to ~150GHz. Not much beyond. 65-32nm nodes are best.

InP HBT: record 100-300GHz PAs

SiGe HBT: power better than CMOS, worse than InP HBT

GaN HEMT: record power below 100GHz. Bandwidth improving

InGaAs-channel HEMT: world's best low-noise amplifiers



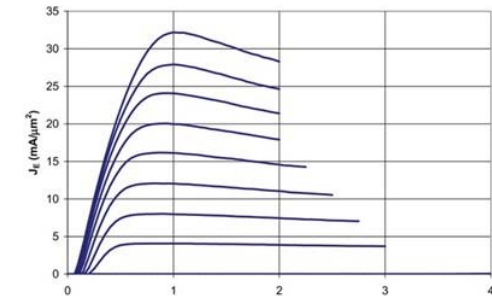
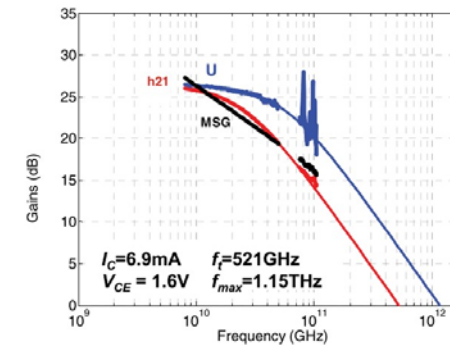
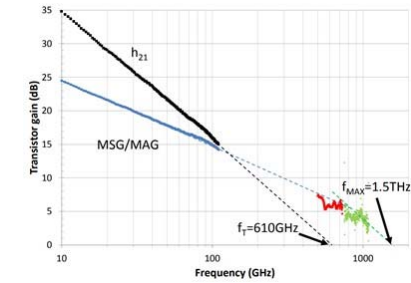
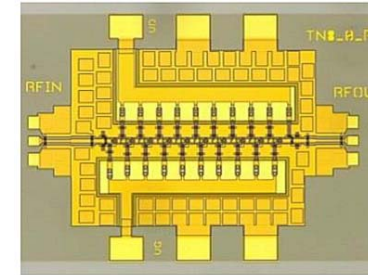
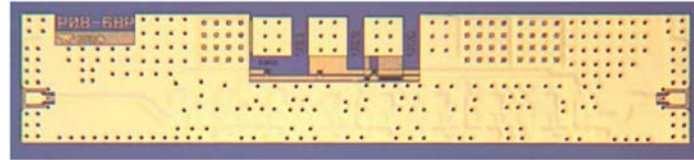
InP Transistors and ICs

InP HEMTs: 1.5THz $f_{\max}$, 1.0THz amplifiers

W. Deal et al, 2016 IEDM (Northrop-Grumman)

130nm InP HBTs: 1.1THz $f_{\max}$, 3.5V. 670 GHz amplifiers

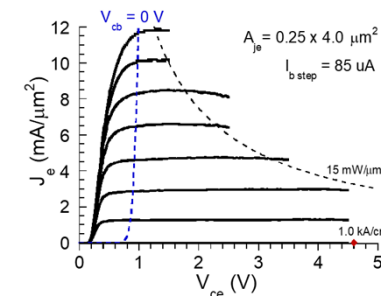
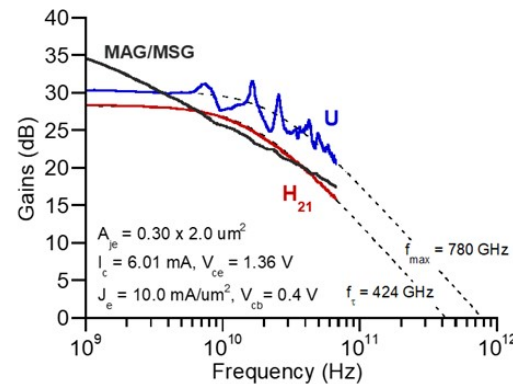
M. Urteaga, et al, IEEE Proceedings June 2017 (Teledyne)



250nm InP HBTs: 650GHz $f_{\max}$, 4.5V.

Z. Griffith et al, 2007 IPRM conference (UCSB)

M. Urteaga, et al, IEEE Proceedings June 2017 (Teledyne)



100-300GHz wireless: transistor requirements

Transmitters need:

high power-added efficiency $PAE = (P_{out} - P_{in})/P_{DC}$

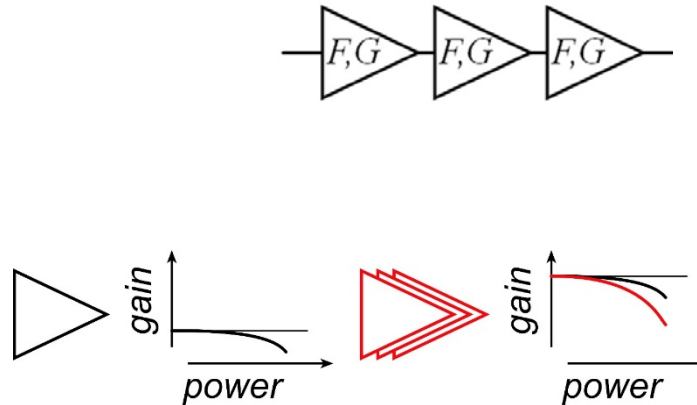
high added power density $(P_{out} - P_{in})/(\text{gate width, emitter length})$

Receivers need:

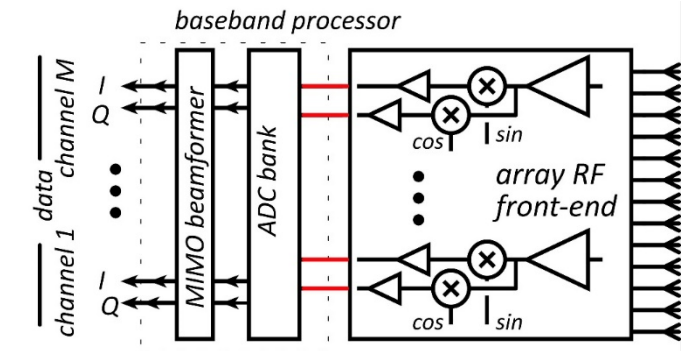
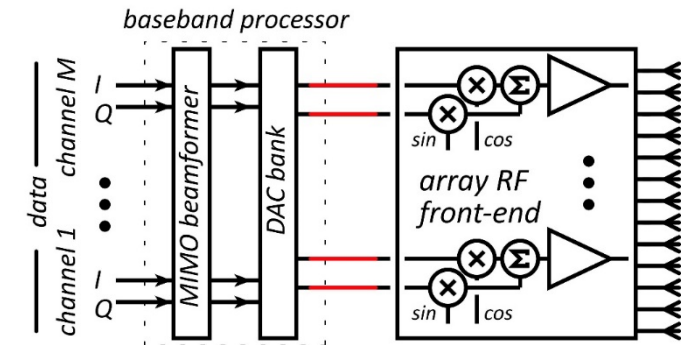
low cascaded noise $F_{casc} = F + (F - 1)/G + (F - 1)/G^2 + \dots$

Need reasonable gain/stage.

die area, power,
accumulated gain compression



(gain in PAs, LNAs is less than MAG/MSG, U, ...)

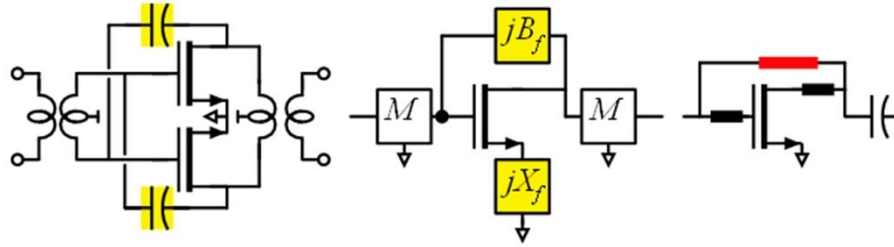
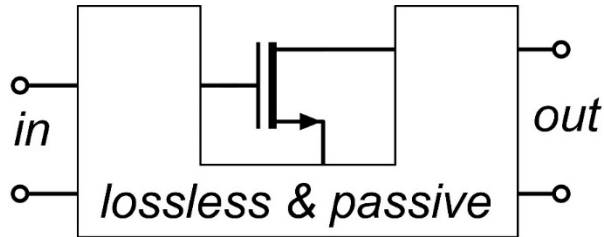


Where the IC designer can't help

mm-wave transistor gain is low: gain-boosting is common

Common-source vs. common-gate.

Capacitive neutralization. Unconditionally stable positive feedback (Singhakowinta, Int. J. Electronics, 1966)



Such circuits don't improve the parameters that matter the most.

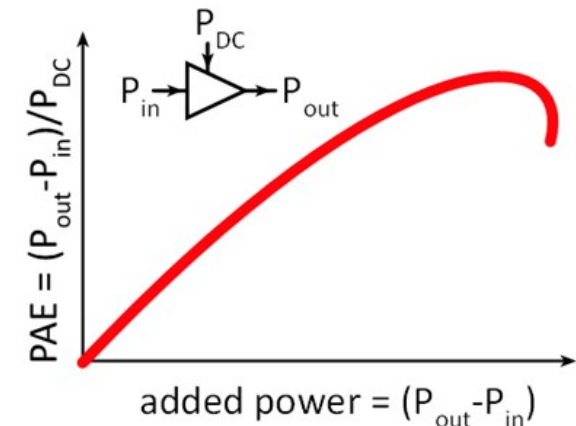
The circuit* doesn't change the **transistor minimum cascaded noise figure**. (Haus, Adler, Proc. IRE, 1958)

The circuit* doesn't change the **transistor maximum efficiency vs. added power curve**.

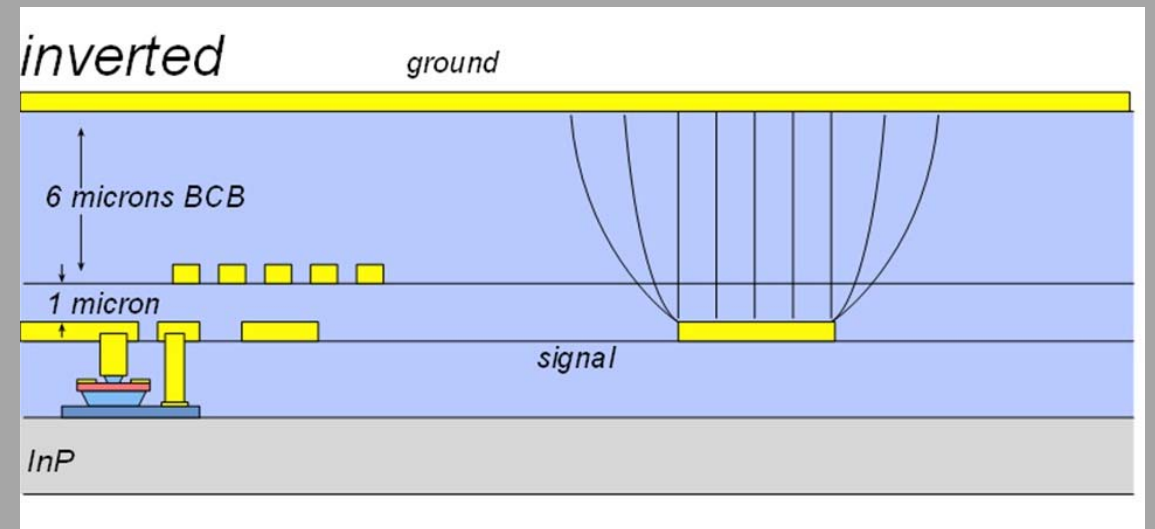
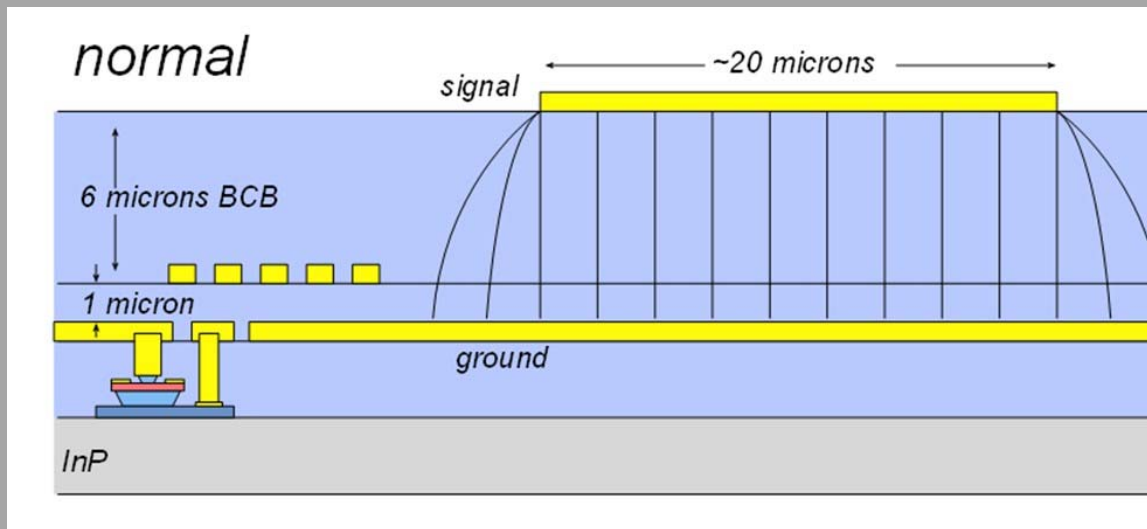


$$F_{casc} = 1 + M = F + (F - 1)/G + (F - 1)/G^2 + \dots$$

*If lossless, and given the correct source and load impedances.



Interconnects

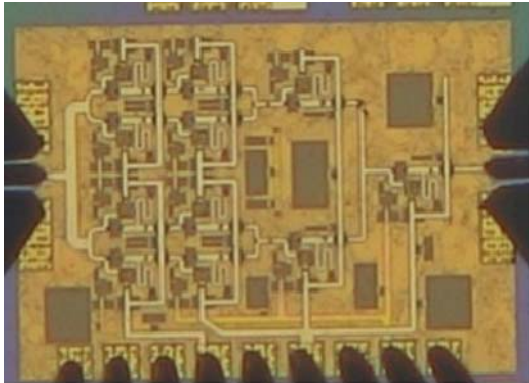
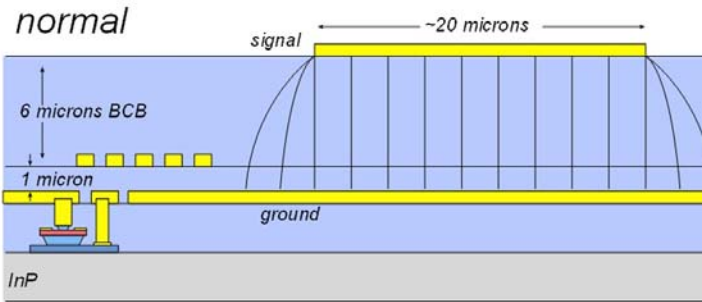


Normal & inverted microstrip

Normal: PAs, LNAs

smaller skin-effect losses ✓

ground-plane holes at transistors ✗

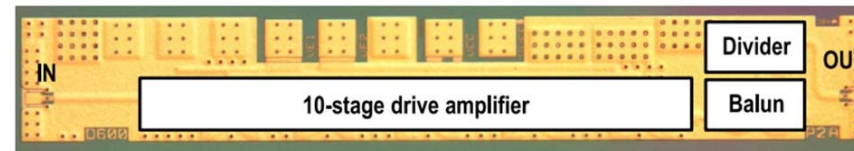
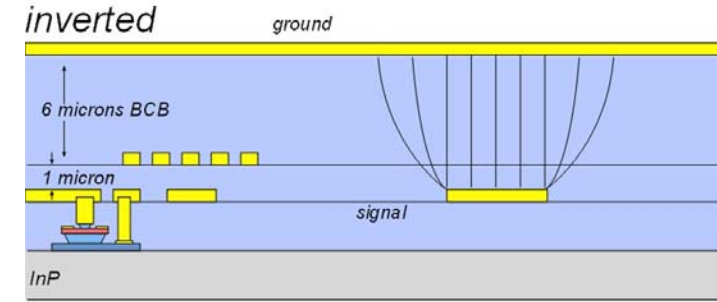


266GHz, 16.8dBm PA: A. Ahmed et. al, 2021 IMS

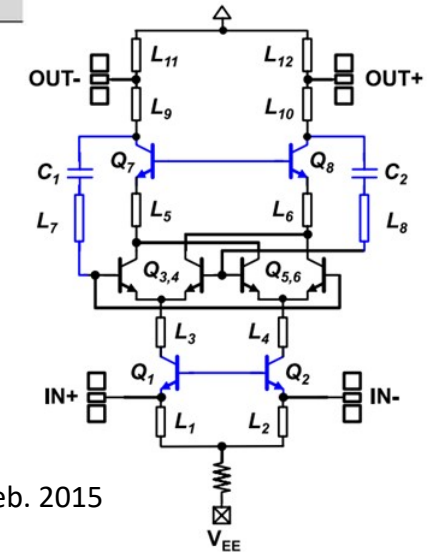
Inverted: high-density blocks (mixers, phase shifters,...)

higher skin-effect losses ✗

no ground-plane breaks: better ground integrity ✓



529GHz dynamic divider: M. Seo et al, IEICE Electronics Express, Feb. 2015



On-Wafer Interconnect Losses

Interconnects in packages and on PCBs:

$H \propto 1/\text{frequency}$ (to control radiation loss)

$\text{loss (dB/mm)} \propto (\text{frequency})^{3/2}$

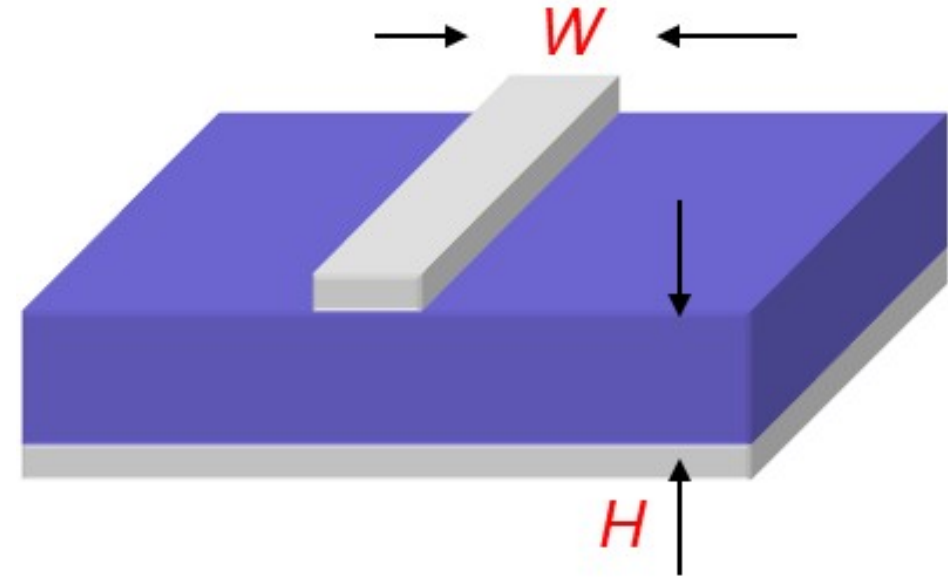
$\text{loss (dB/wavelength)} \propto \sqrt{\text{frequency}}$

Interconnects in ICs:

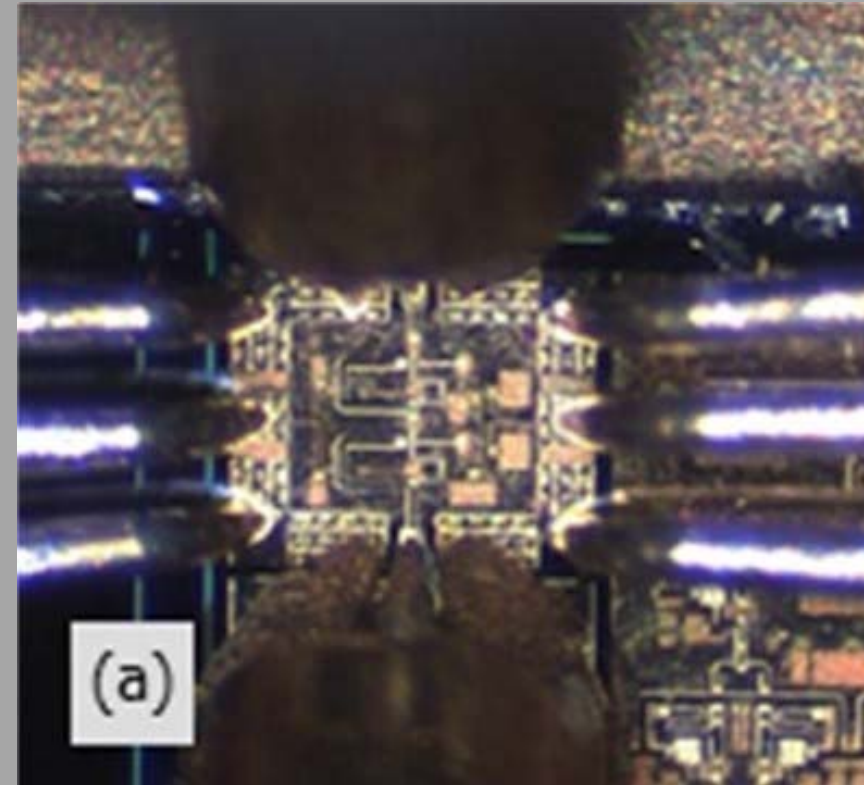
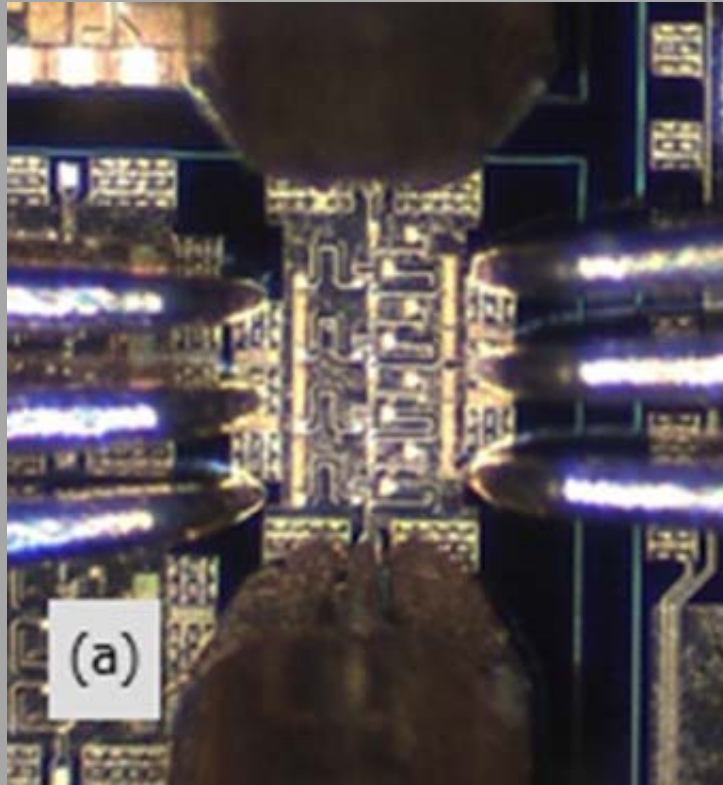
H is independent of frequency

$\text{loss (dB/mm)} \propto \sqrt{\text{frequency}}$

$\text{loss (dB/wavelength)} \propto 1/\sqrt{\text{frequency}}$

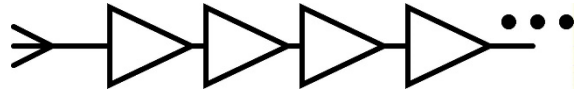


Low-Noise Amplifiers



LNA design: noise close to transistor limits

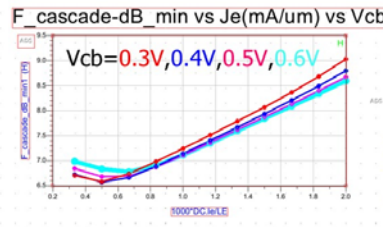
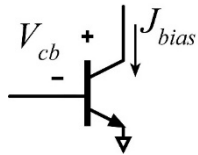
- 1) Goal: low **noise measure**, not **noise figure**



$$F_{\text{cascade}} = M + 1 = F + \frac{F-1}{G} + \frac{F-1}{G^2} + \dots = \frac{F-1/G}{1-1/G}$$

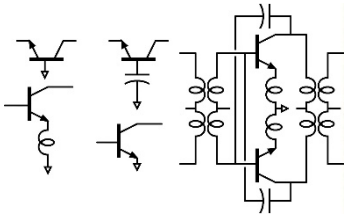
F = noise figure, M = noise measure

- 2) Find bias current density for lowest **noise measure**



@210GHz,
 $F_{\text{cascade,min}} = 6.57 \text{ dB}$
 given:
 $J_e = 0.5 \text{ mA/um}$,
 $V_{cb} = 0.3 \text{ V}$

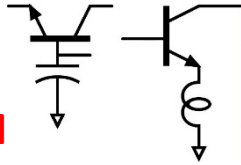
- 3) Minimum **M** is **independent of circuit configuration***;
 pick for high bandwidth or high gain/stage (= low P_{DC})



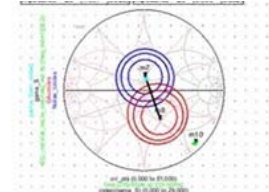
<-- all give the same minimum M ...
 ...but **common-base** gives highest gain
 (InP HBT @210GHz).

*HA Haus, RB Adler, Proceedings of the IRE, 1958

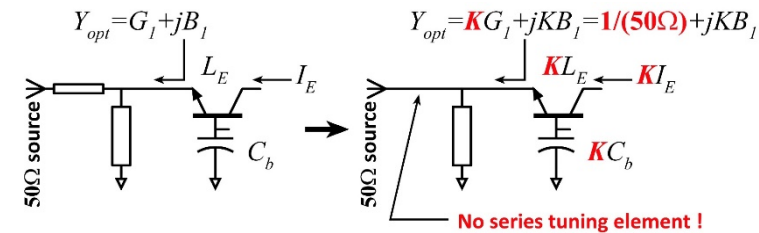
- 4) **Capacitance** in **common-base**; just like
inductance in **common-emitter**, allows simultaneous
 tuning for **zero reflection coefficient** and minimum **M**



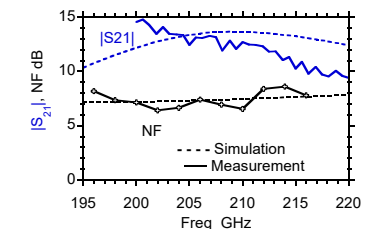
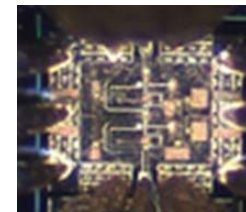
- 5) Write **ADS Python code** to display
 source impedance for minimum **M**.



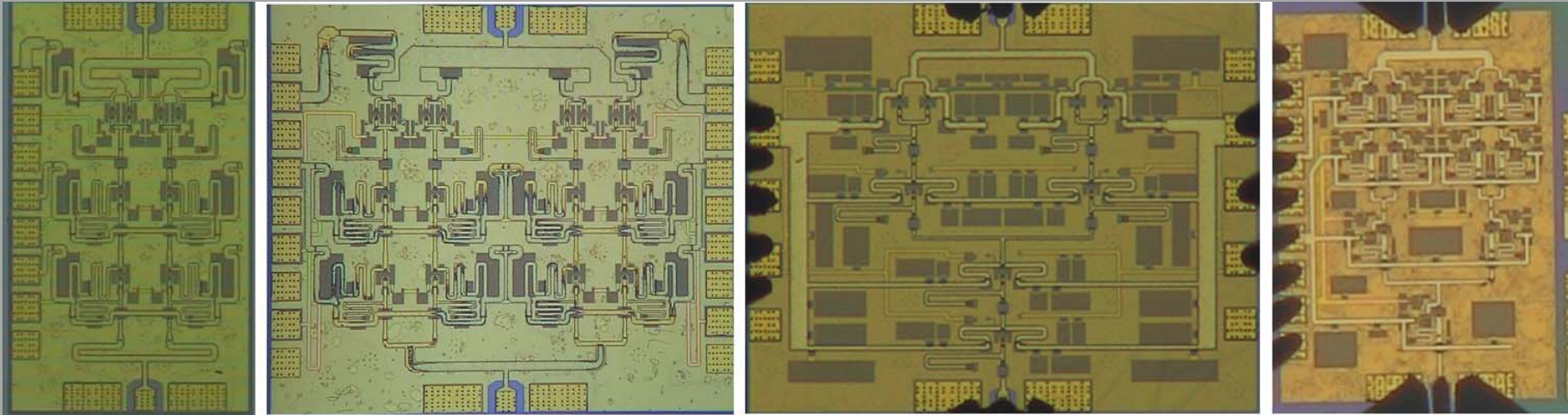
- 6) **Scale transistor size** to **eliminate series tuning element**.
 Less input tuning → less noise from passive element loss.



Result: 7.2-7.4dB LNA noise given 6.6dB transistor F_{cascade}

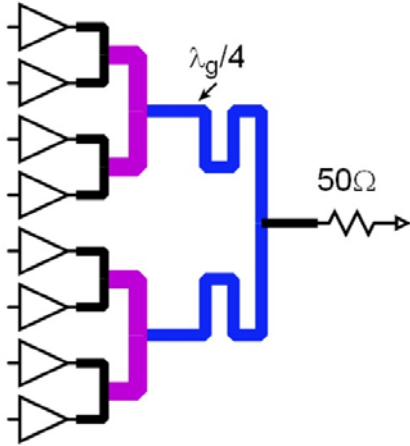


Power Amplifiers



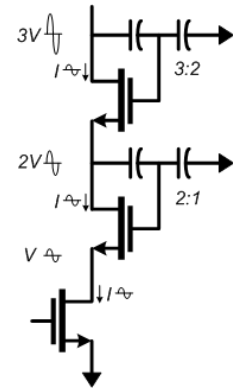
100-300GHz Power combining: what is best ?

Corporate T-line



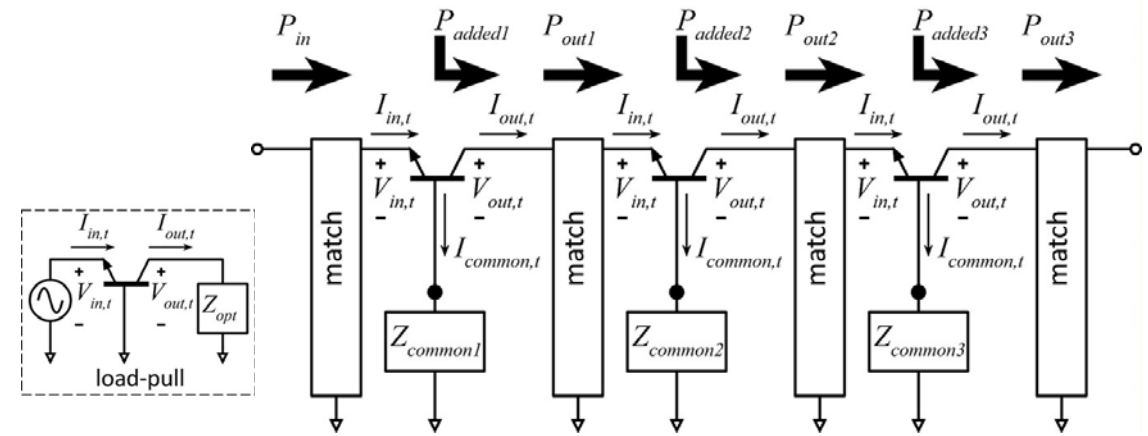
Direct series-connected

M. Shifrin: 1992 IEEE μ Wave/mmWave Monolithic Circuits Symp. (Raytheon)



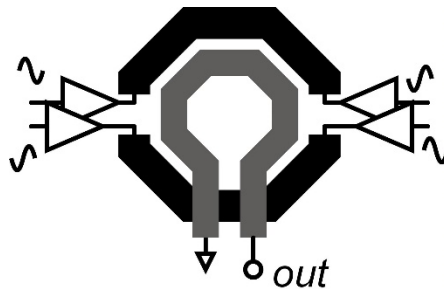
Cascaded combining

A. Ahmed 2018 EuMIC, 2021 RFIC (UCSB)



Distributed Active Transformer

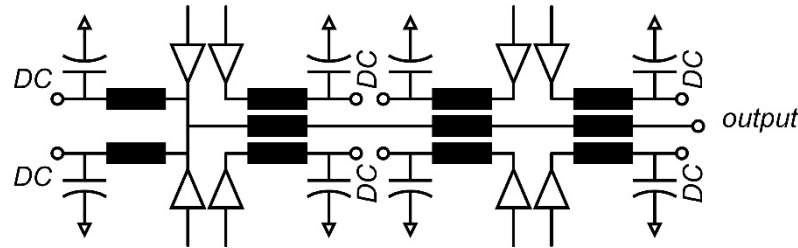
I. Aoki, IEEE Trans MTT, Jan. 2002 (CalTech)



Balun series-connected

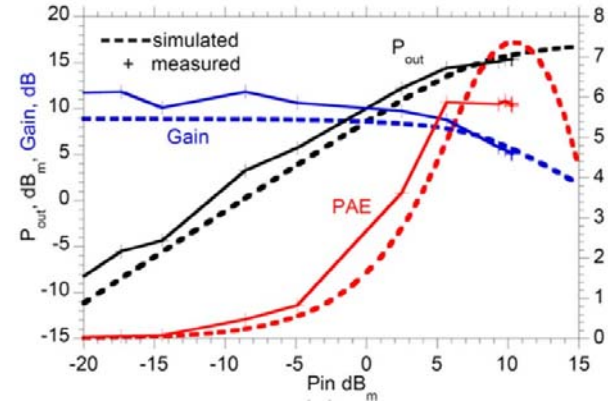
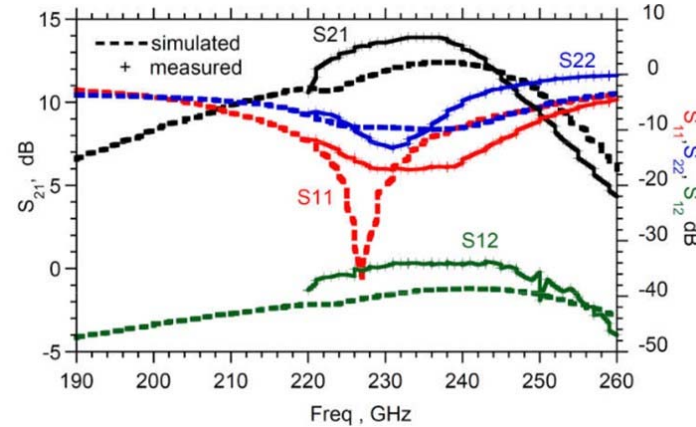
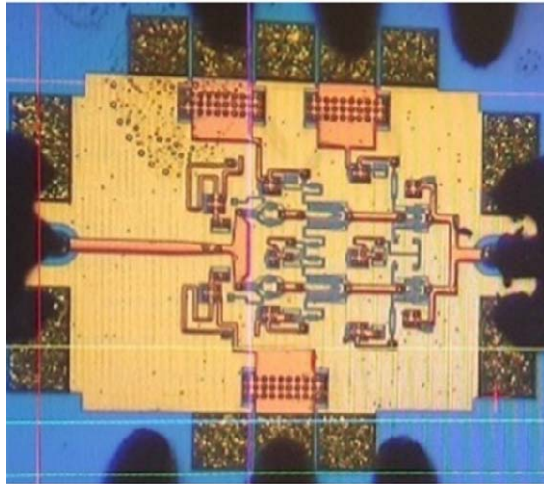
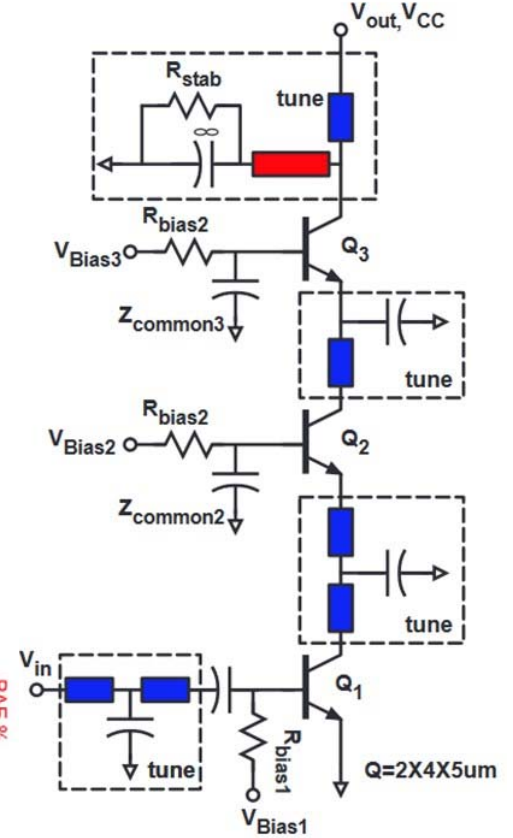
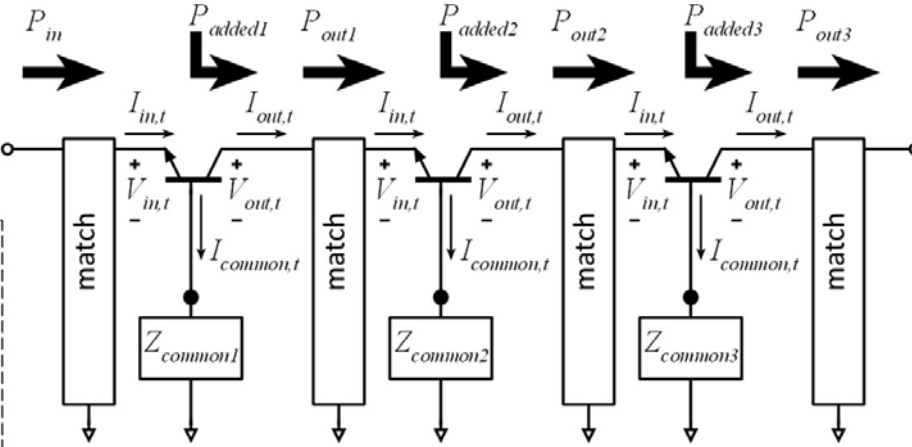
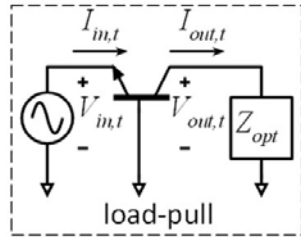
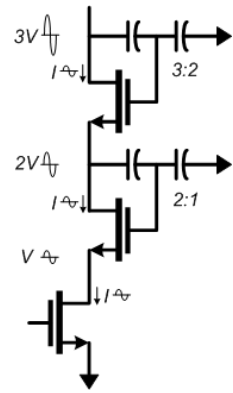
$\lambda/4$ baluns: Y. Yoshihara, 2008 IEEE Asian Solid-State Circuits Conference (Toshiba)

$\text{sub-}\lambda/4$ baluns: H. Park, et al, IEEE JSSC, Oct. 2014 (UCSB)

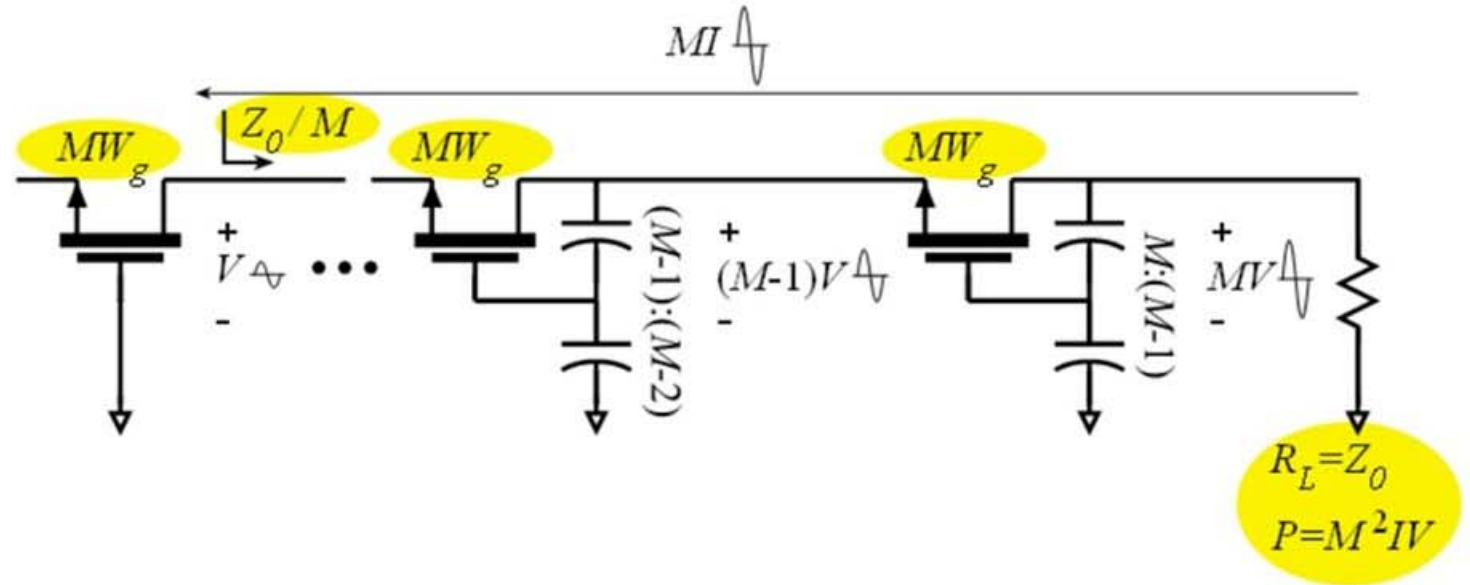
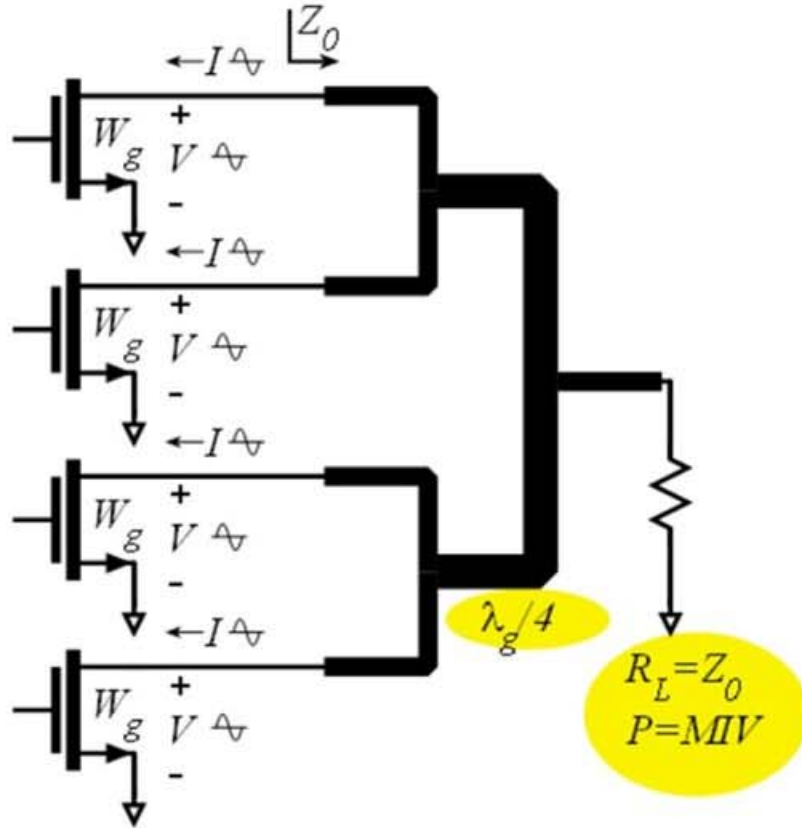


Cascade combining as stacking plus matching

A. S. H. Ahmed et al, 2018 EuMIC (UCSB)



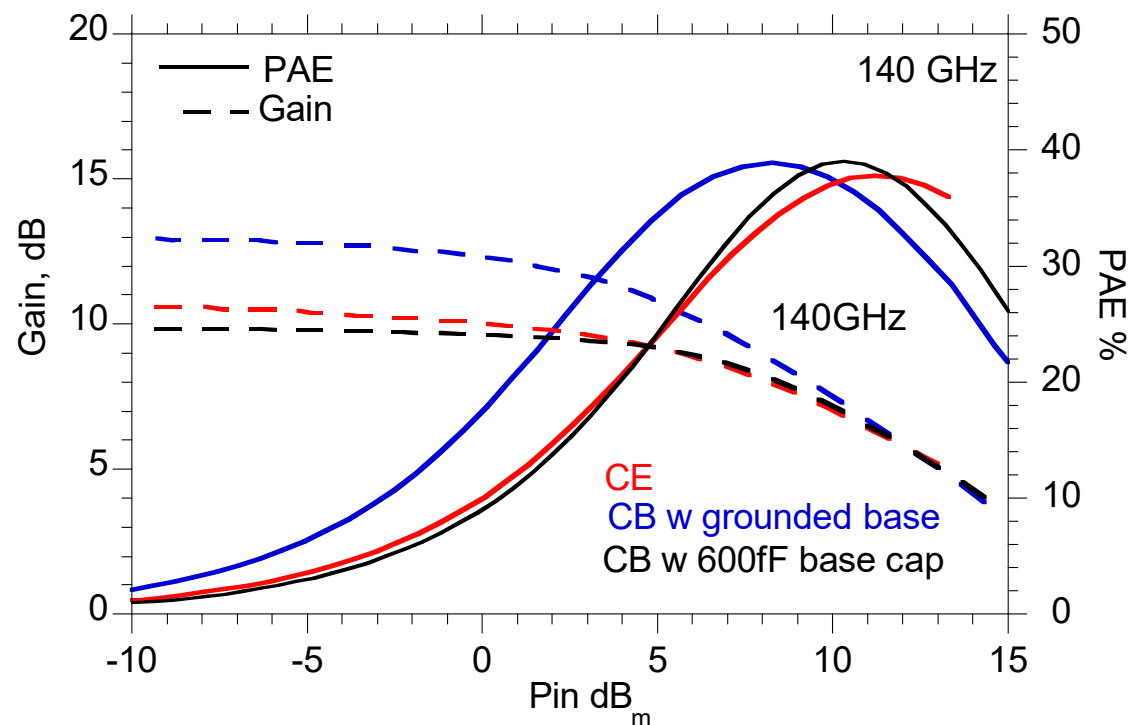
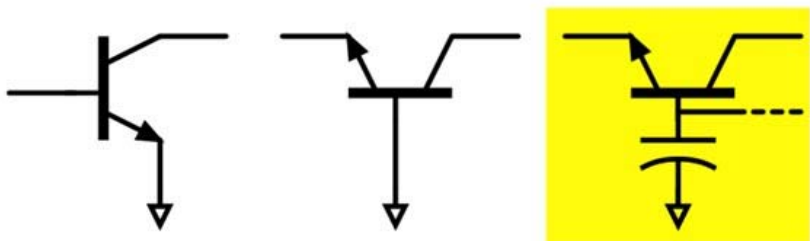
Transistor stacking. Why ? Why not ?



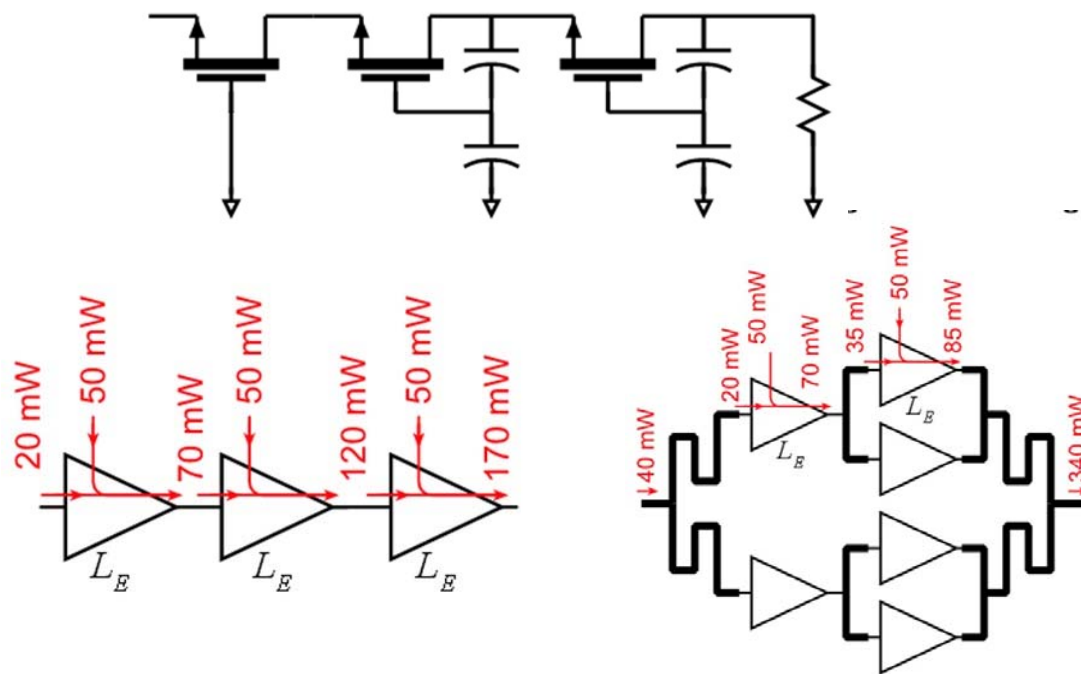
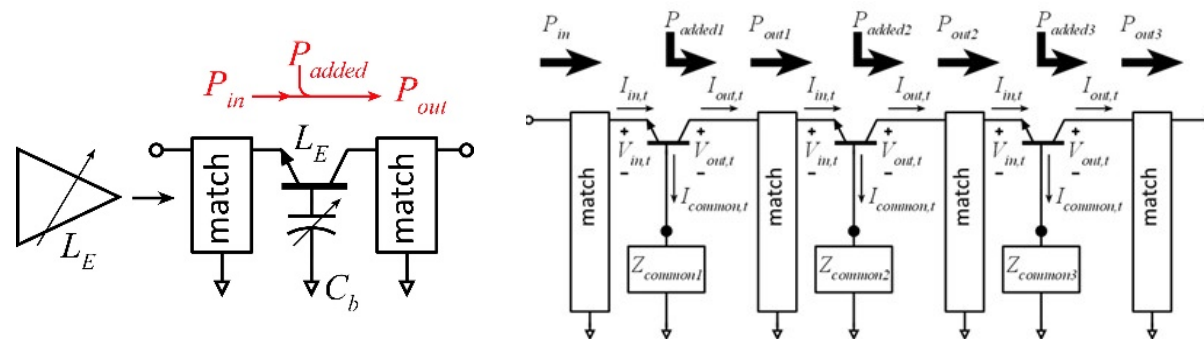
	Lower frequencies	Higher frequencies
Corporate combining	length $\propto 1/f \rightarrow$ large die area $\times$ dB loss $\propto 1/\sqrt{f} \rightarrow$ high loss $\times$	length $\propto 1/f \rightarrow$ small die area $\checkmark$ dB loss $\propto 1/\sqrt{f} \rightarrow$ low loss $\checkmark$
Series-connected	more transistor fingers per cell $\rightarrow$ ok $\checkmark$	more transistor fingers per cell $\rightarrow$ parasitics $\times$

Capacitively degenerated common-base

Lower gain, same peak PAE, higher PAE at P_{1dB} .



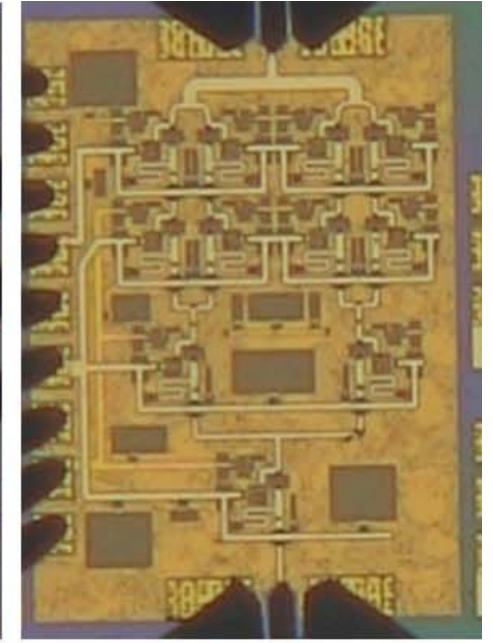
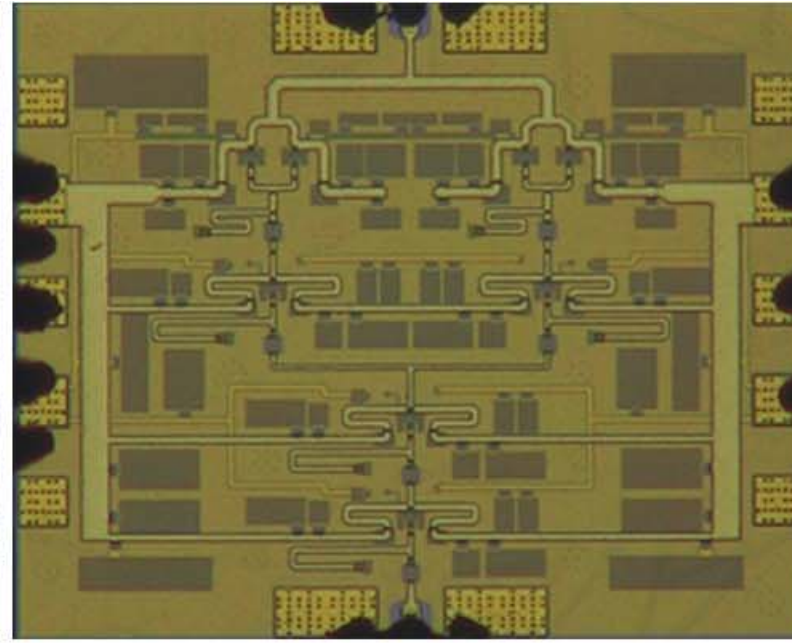
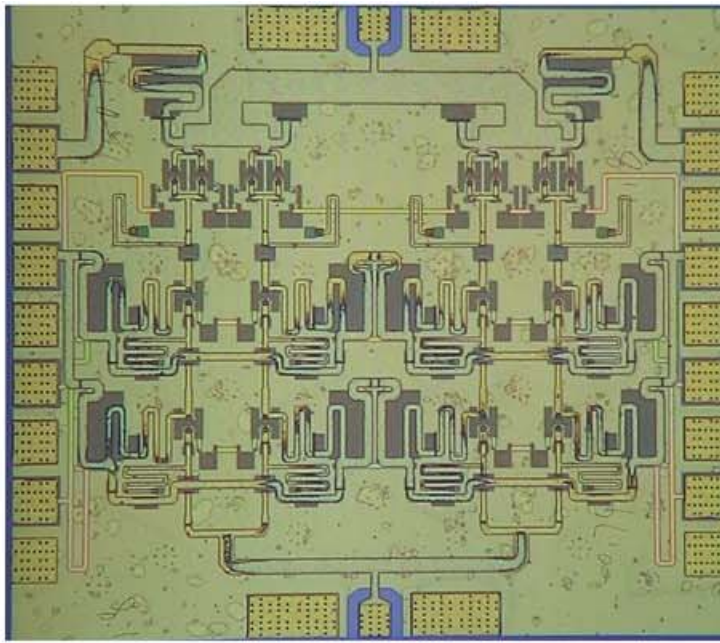
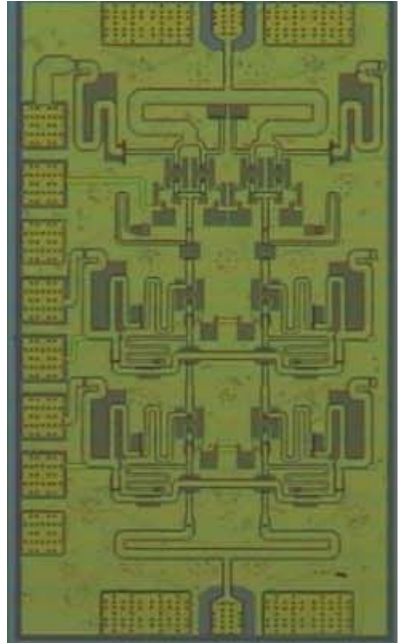
How does this differ from stacking?



Recent high-efficiency 100-300GHz PAs

Teledyne 250nm InP HBT technology

Ahmed et al, 2020 IMS, 2020 EuMIC, 2021 IMS, 2021 RFIC

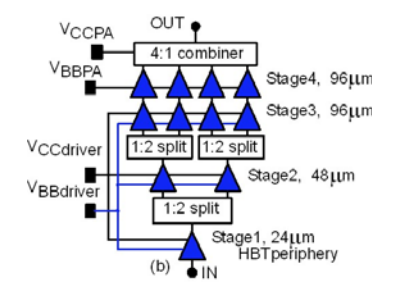
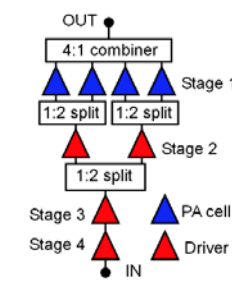
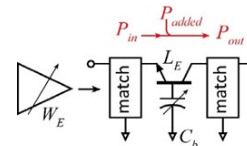
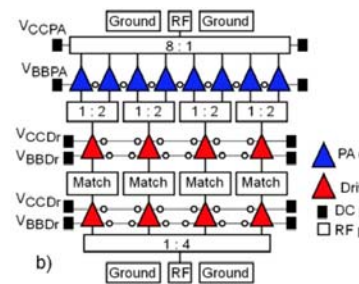
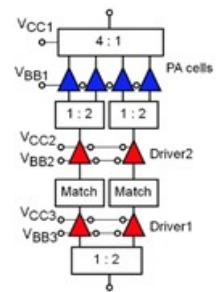


140GHz, 20.5dBm, 20.8% PAE

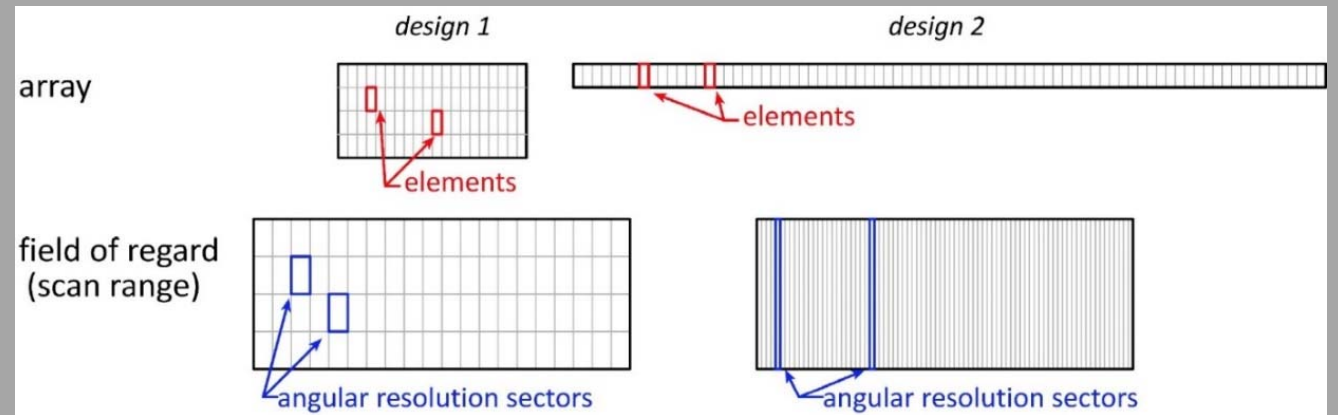
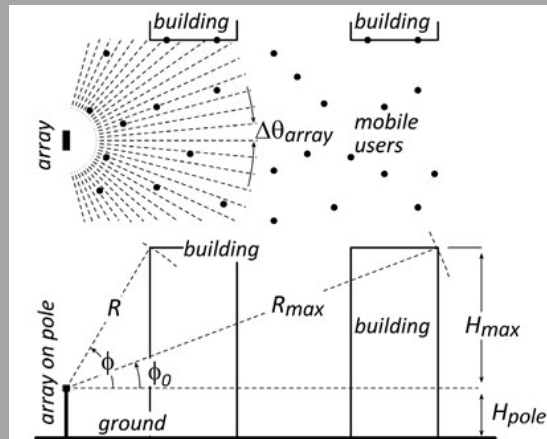
130GHz, 200mW, 17.8% PAE

194GHz, 17.4dBm, 8.5% PAE

266GHz, 16.8dBm, 4.0% PAE



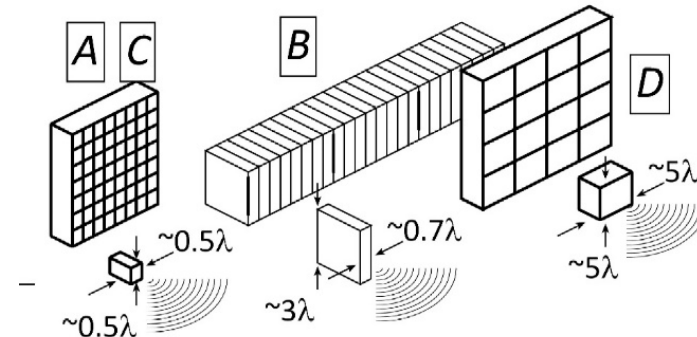
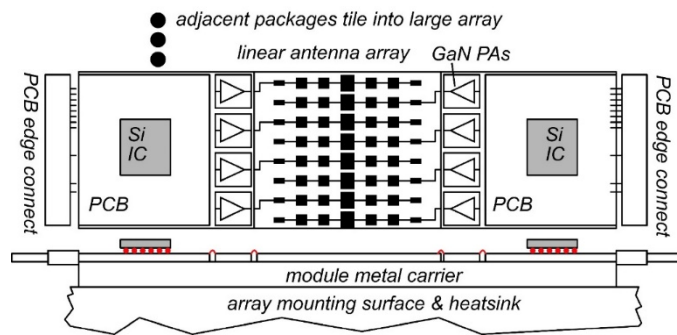
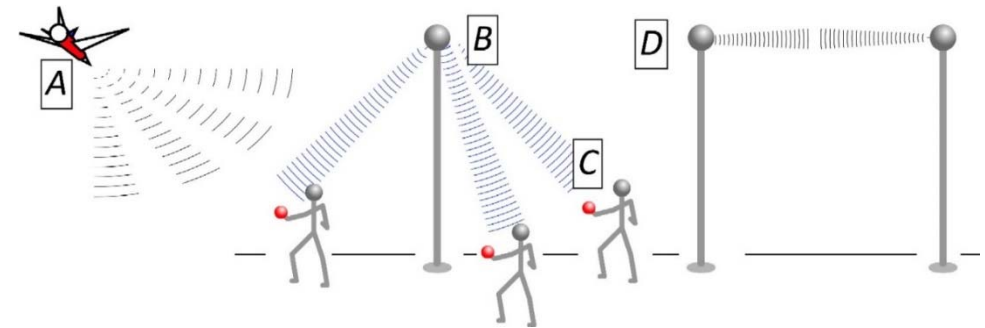
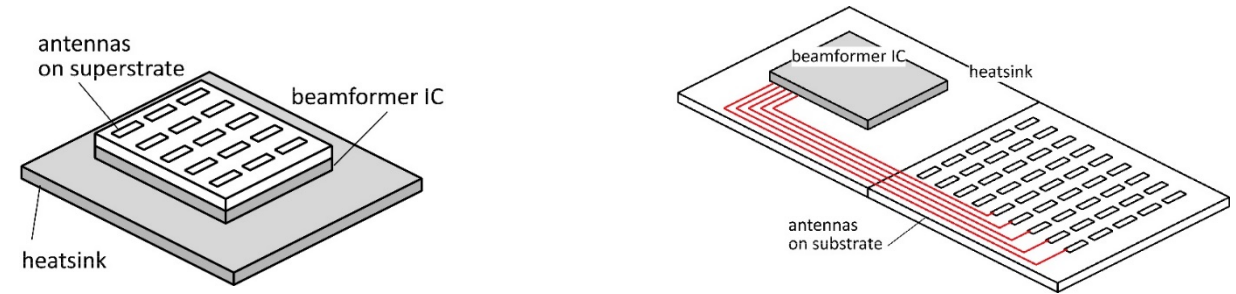
1D and 2D Array Design



The mm-wave module design problem

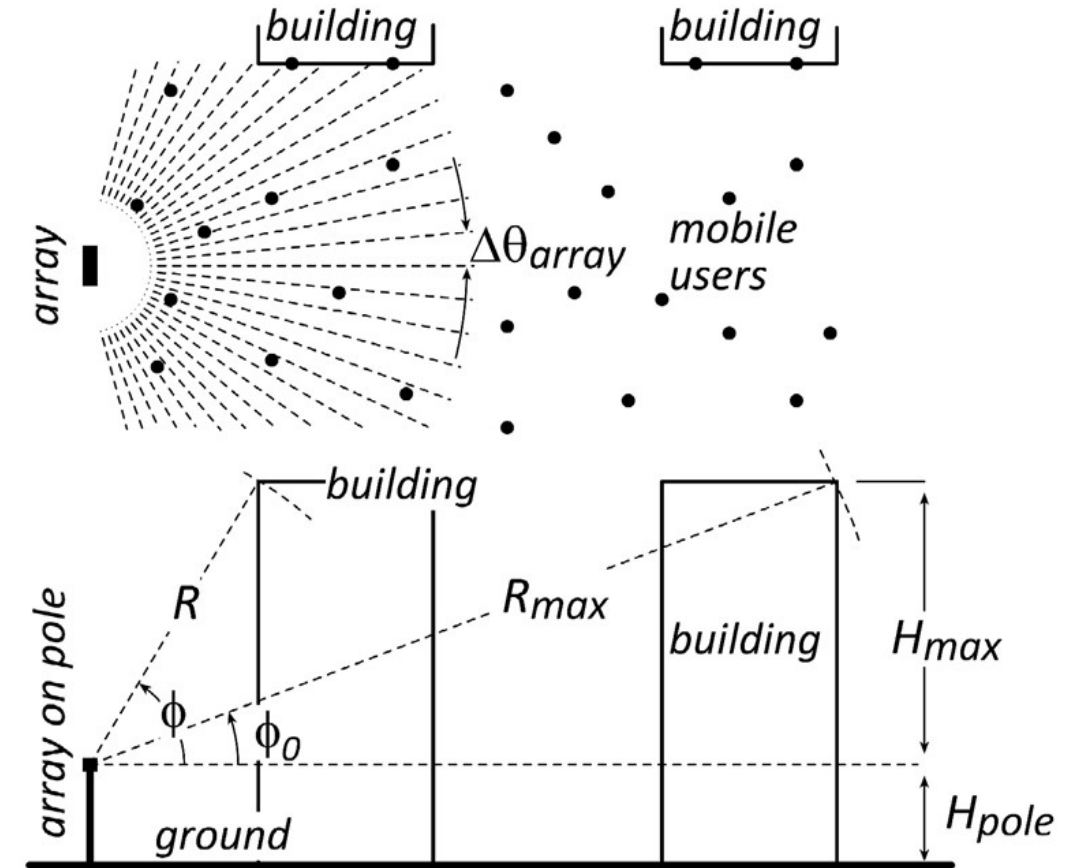
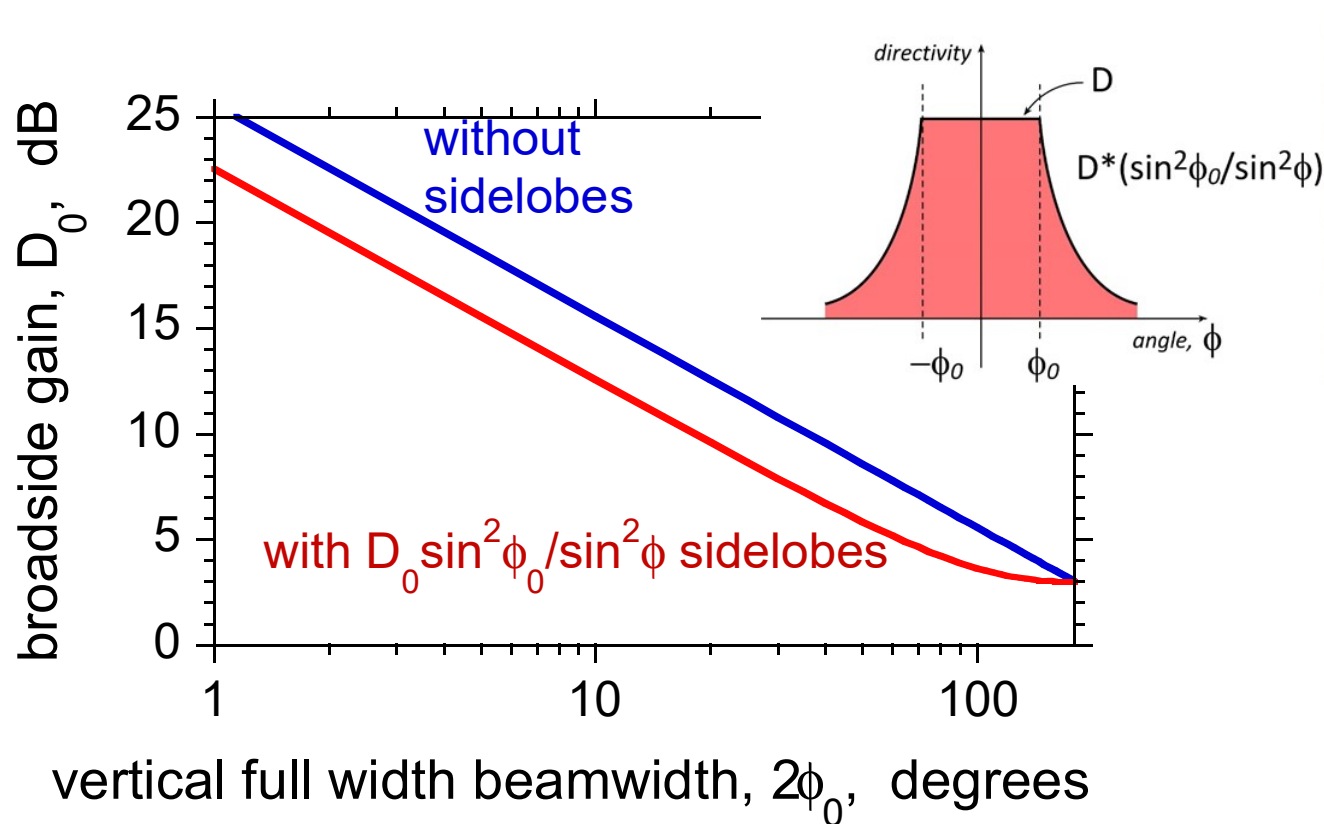
How to make the IC electronics fit ?
How to avoid catastrophic signal losses ?
How to remove the heat ?

Not all systems steer in two planes...
...some steer in only one.
Not all systems steer over 180 degrees...
...some steer a smaller angular range

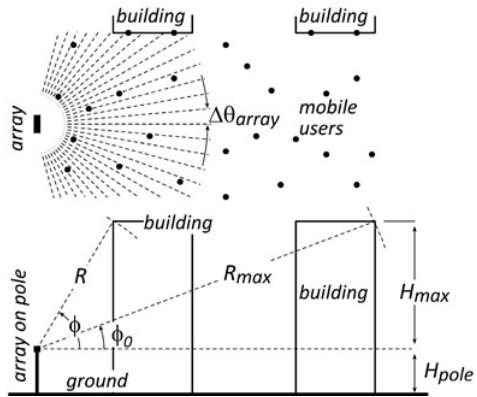


Do we need 2D arrays ? 1D might be fine.

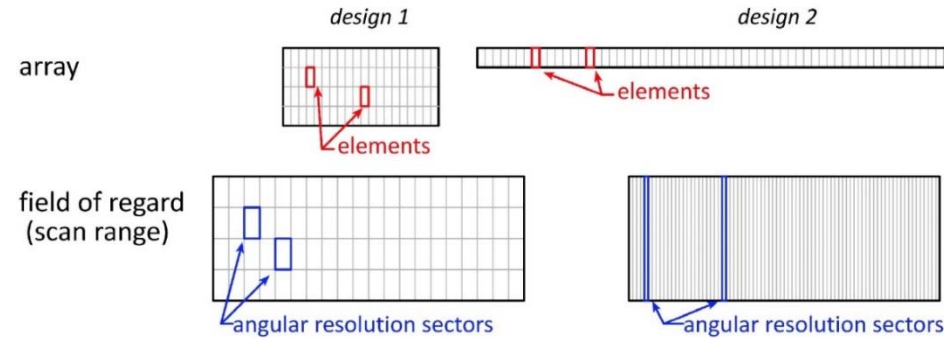
$1/\sin^2\phi$ sidelobes provide strong signals to tall buildings.
Providing sidelobes reduces broadside gain by less than 3dB.
→ Don't need 2D arrays to serve tall buildings



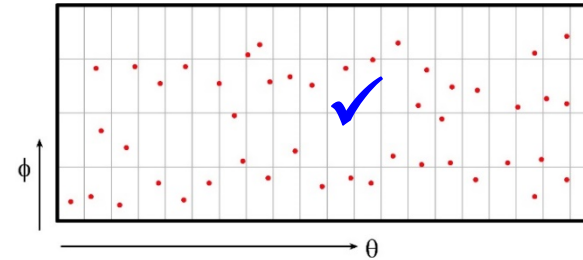
2D vs. 1D: user spatial distribution



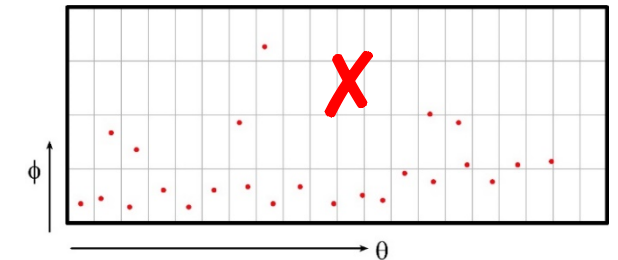
design 1: 2D array



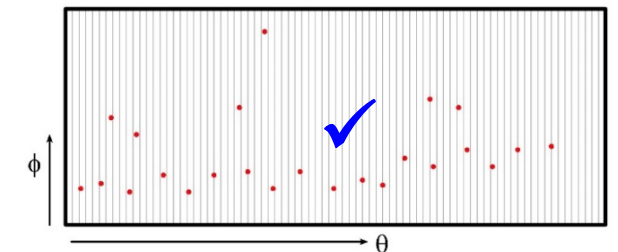
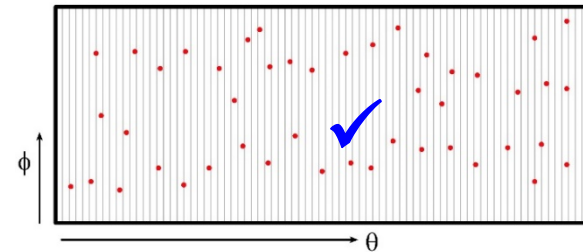
uniform horizontal & vertical user distributions



uniform horizontal, nonuniform vertical



design 2: 1D array

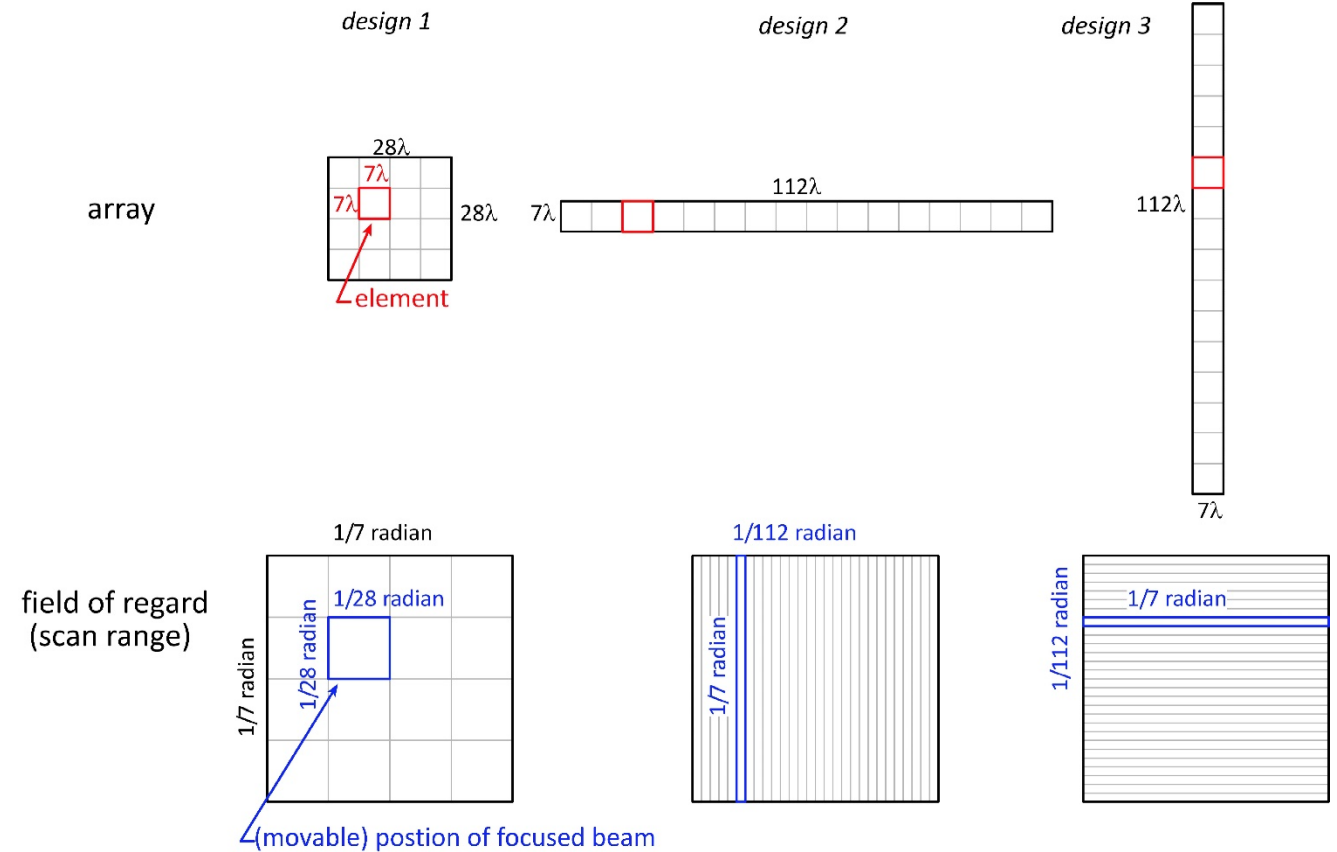
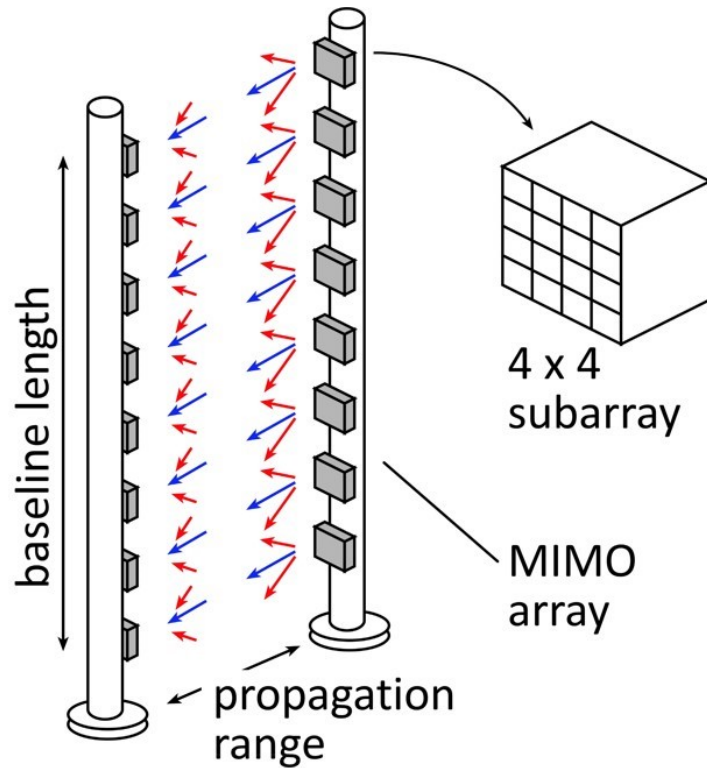


Spatial distribution of users, and of scattering objects, guides choice of array geometry.

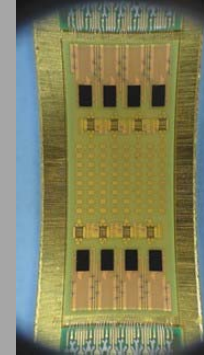
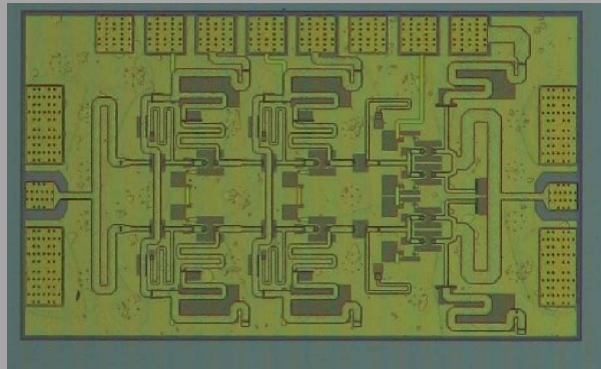
1D or 2D subarray for backhaul ?

Should we use 4x4 array, 1x16, or 16x1 array ?

All provide same system link budget, same # RF channels, same angular scanning range.

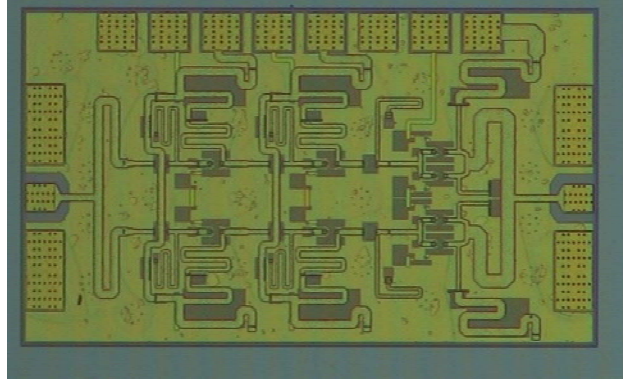


140 GHz Array Modules

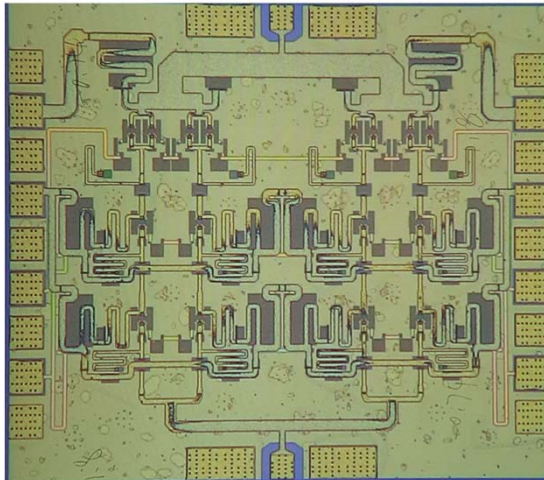


Gen. I 140GHz MIMO hub modules

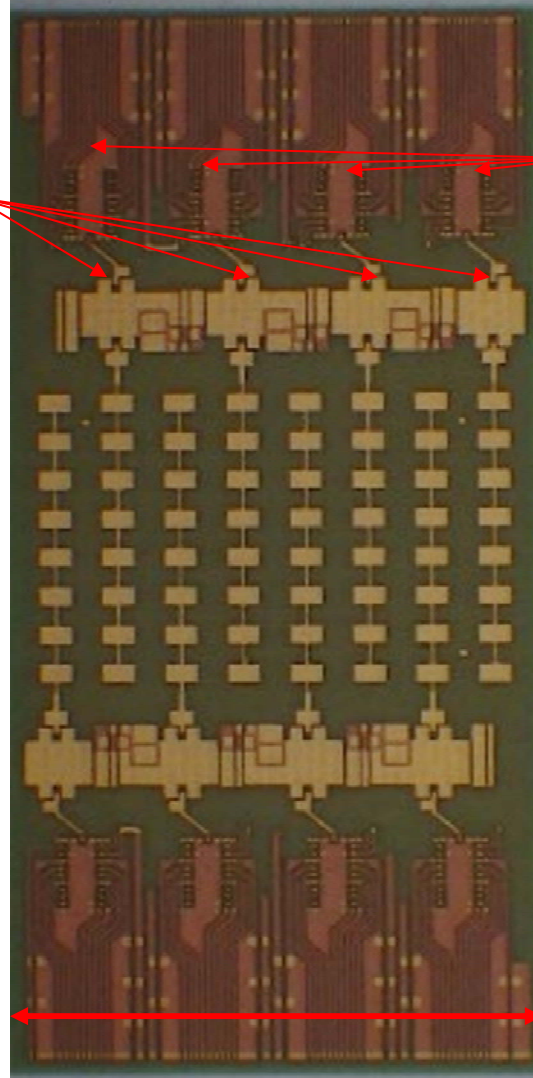
110mW InP Power Amplifier^a LTCC Array module
20.8% PAE



190mW InP Power Amplifier^b
16.7% PAE

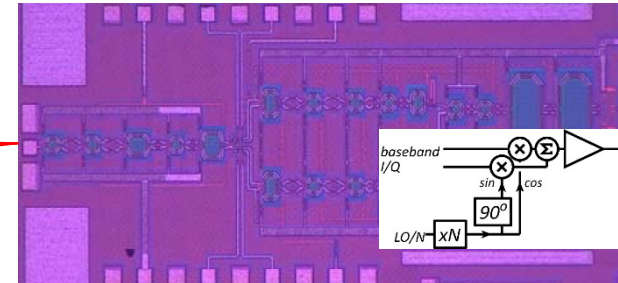


Teledyne 250nm InP HBT

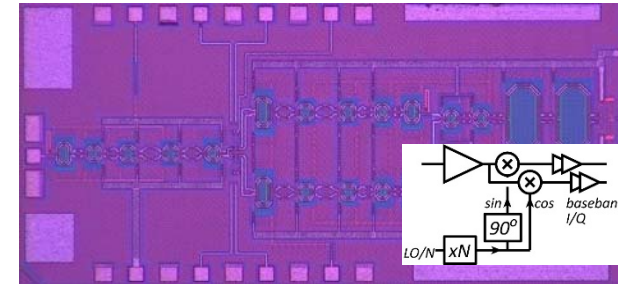


Kyocera

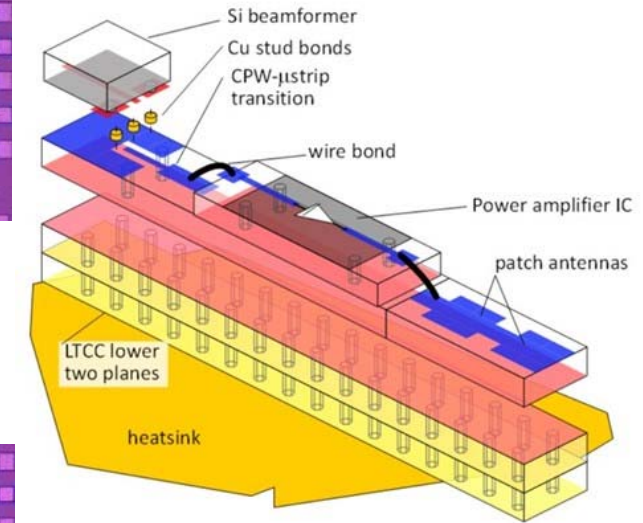
CMOS Transmitter IC^c
22nm SOI CMOS.



Receiver IC^c
22nm SOI CMOS.



GlobalFoundries 22nm SOI CMOS

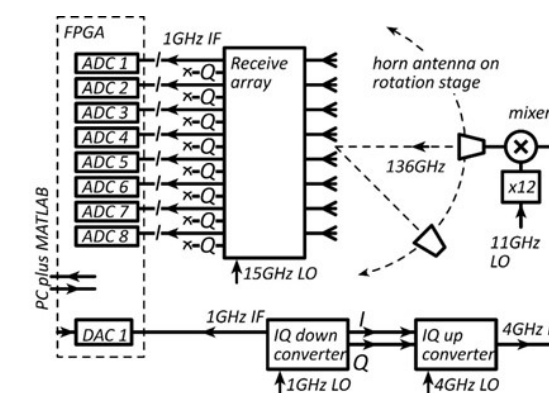
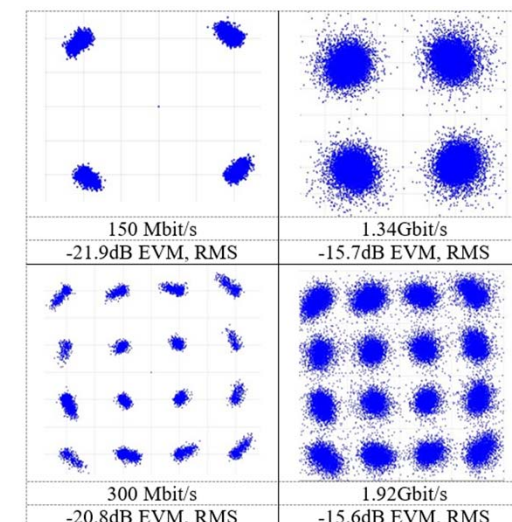
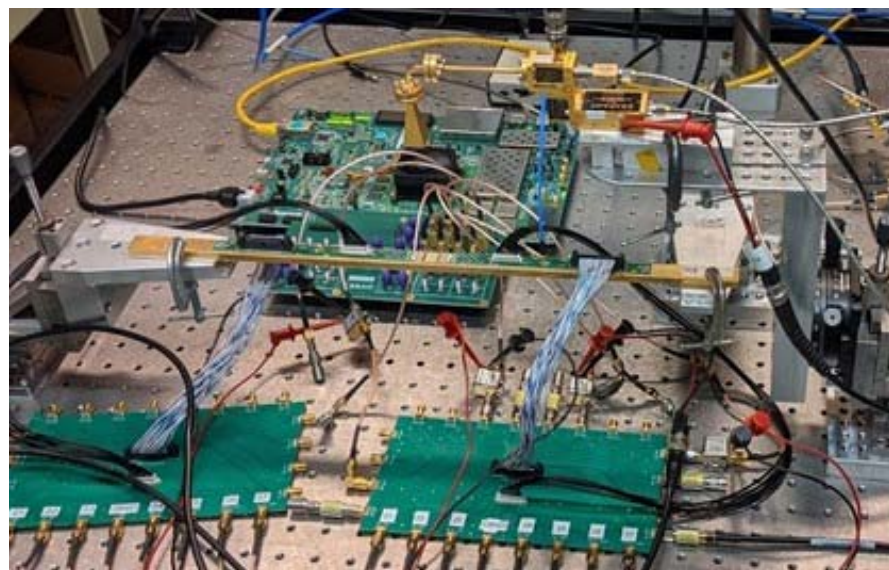
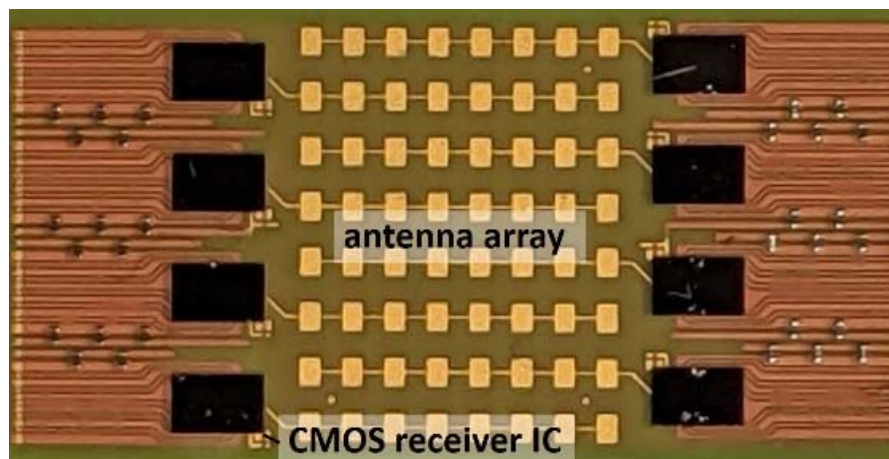
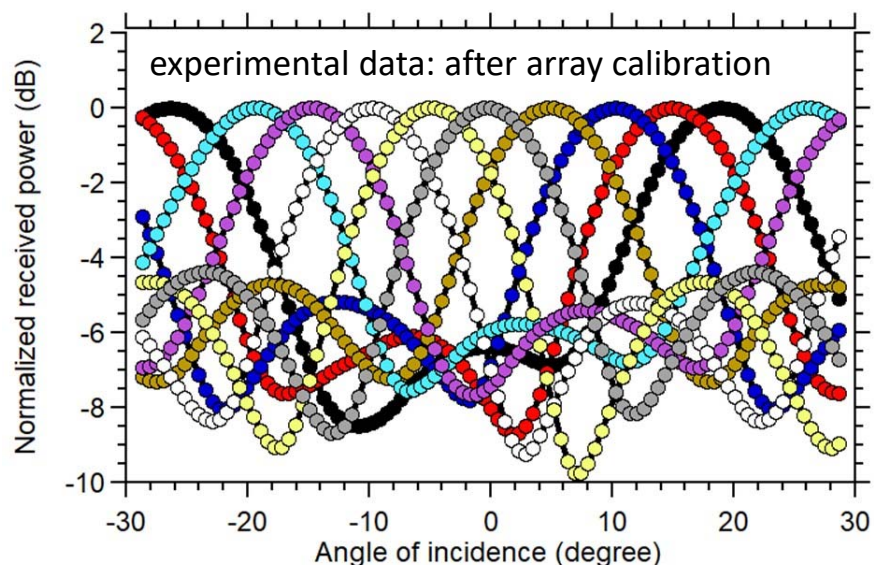
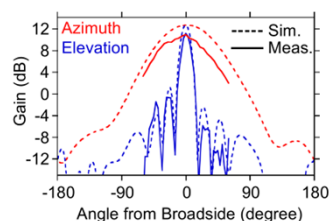


- (a) A. S. H. Ahmed et al., 2020 IMS
(b) A. S. H. Ahmed et al., 2021 EuMIC
(c) A. Farid et al., 2019 RFIC

Gen. I 140GHz MIMO hub receivers

A. Farid et. al, 2021 IEEE BCICTS

Demonstrated MIMO beamforming
Demonstrated 1.9Gb/s 16QAM transmission
Baseband connector limits data rate
Low assembly yield: ~60% working channels on most modules



Gen. I 140GHz MIMO hub transmitters

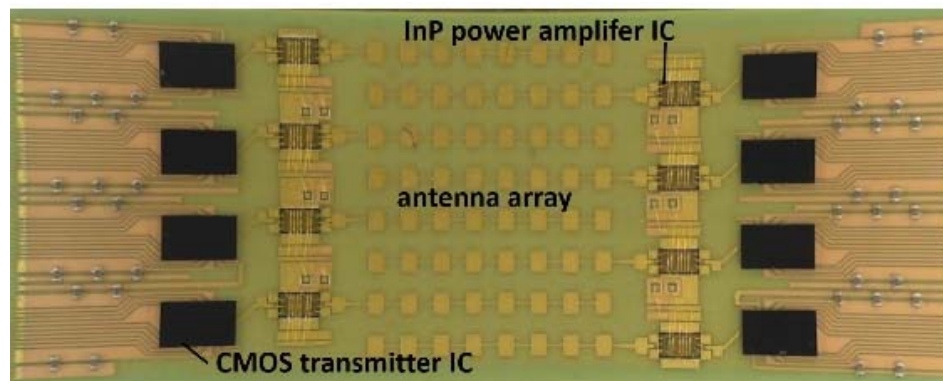
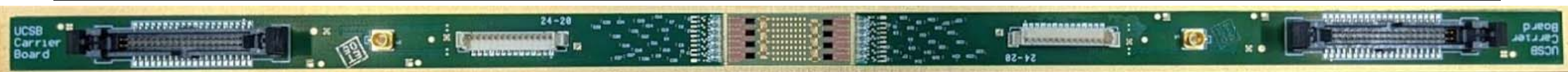
A. Farid et. al, IEEE Trans. MTT 4/2022

Demonstrated 1.9Gb/s 16QAM transmission

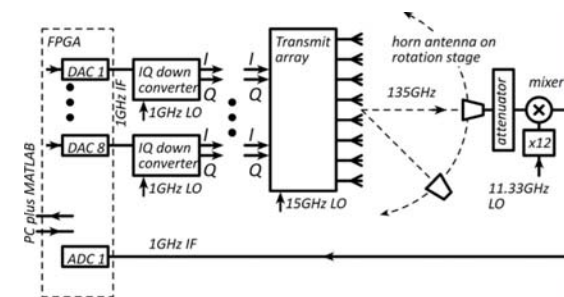
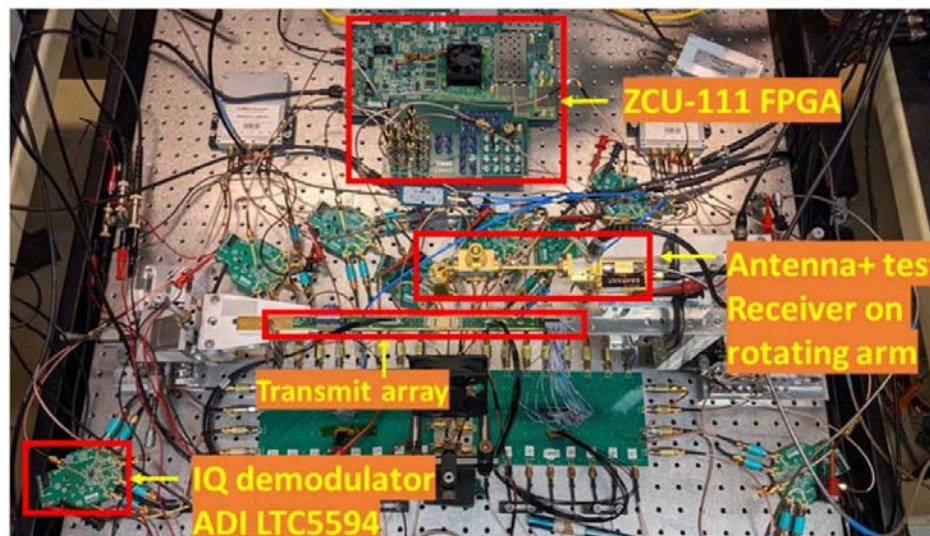
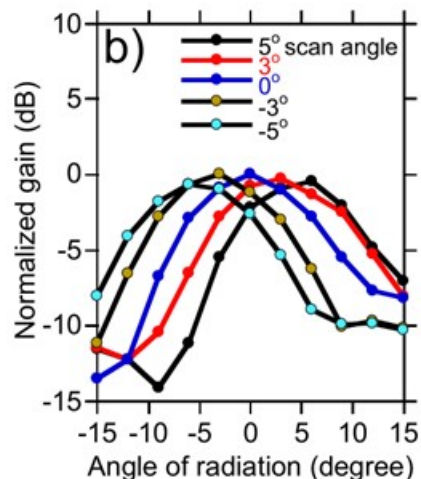
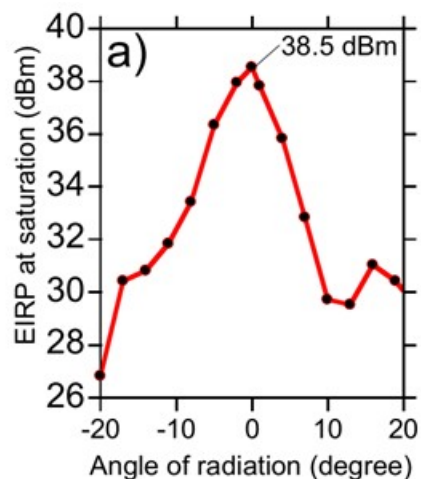
Baseband connector limits data rate

Low assembly yield: ~50% working channels

Degrades beamsteering, EIRP, MIMO operation

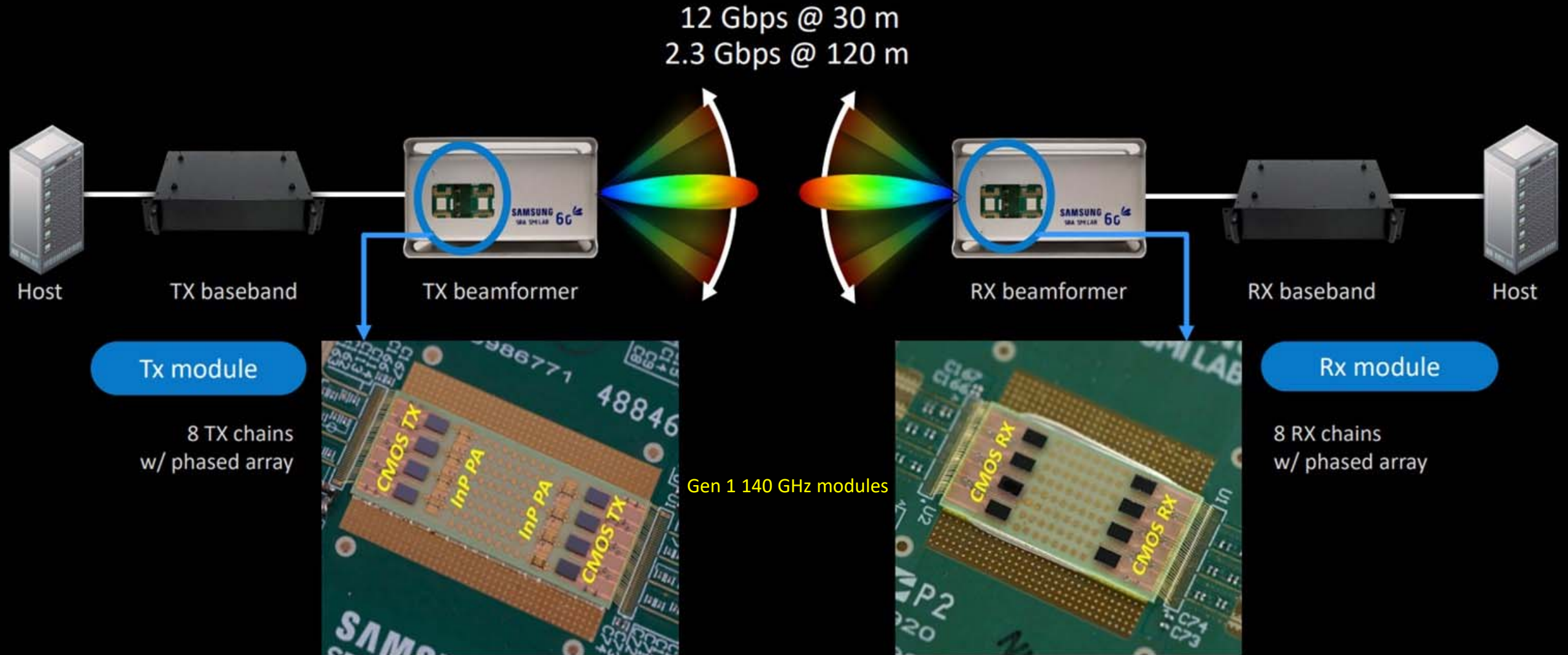


EIRP=35 dBm/ 3 dB Back off from P_{sat}	
QPSK (150 Mb/s)	16QAM (300 Mb/s)
-23 dB EVM (RMS)	-20.5 dB EVM (RMS)
QPSK (1.34 Gb/s)	16QAM (1.92 Gb/s)
-13.5dB EVM (RMS)	-13dB EVM (RMS)



Samsung/ComSenTer 140 GHz Link Demo

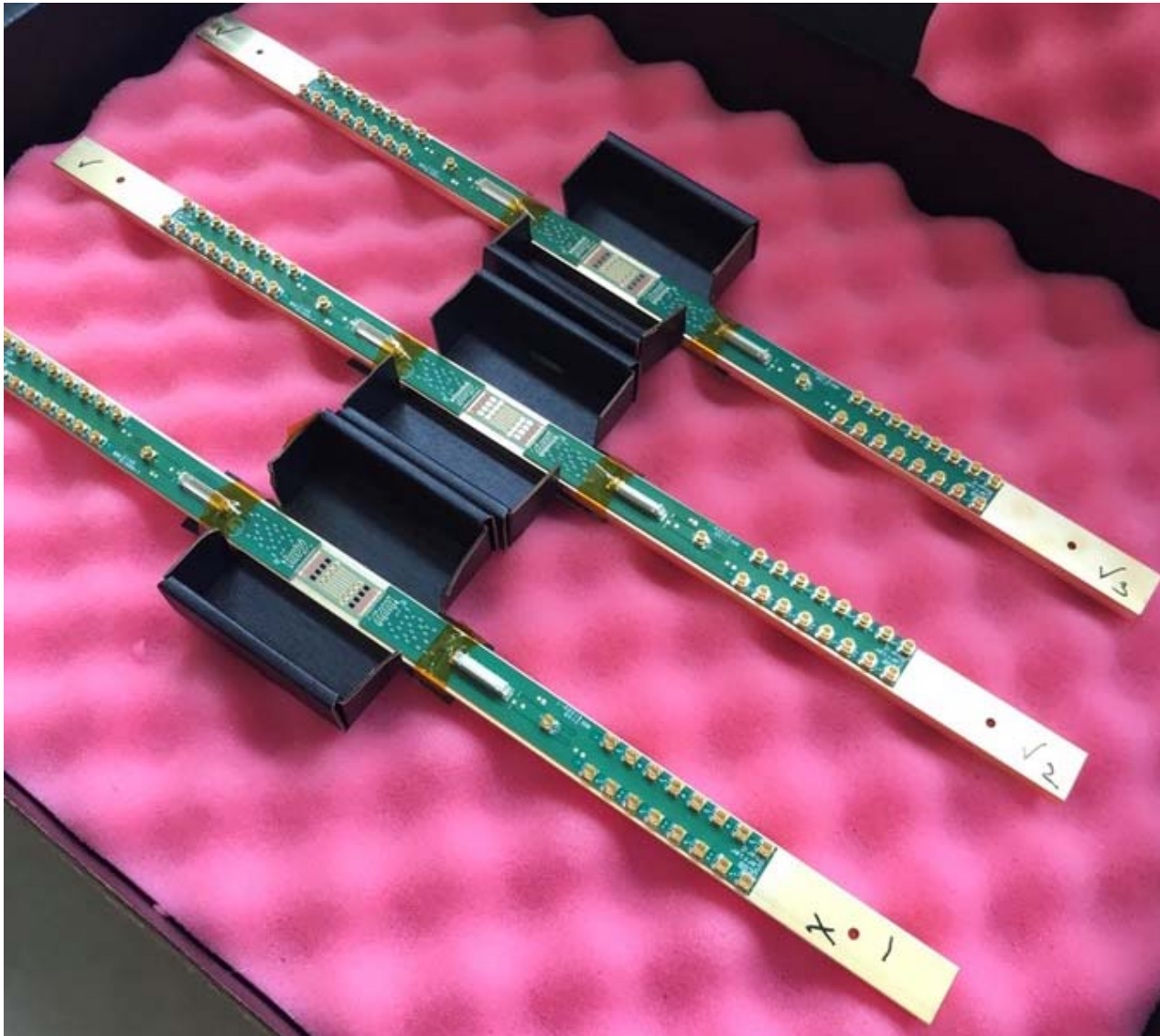
Teflon lens used to extend link range



Abu-Surra et. al. (Samsung) 2022 IEEE International Conference on Communications, 16 -20 May 2022, Seoul, Korea,

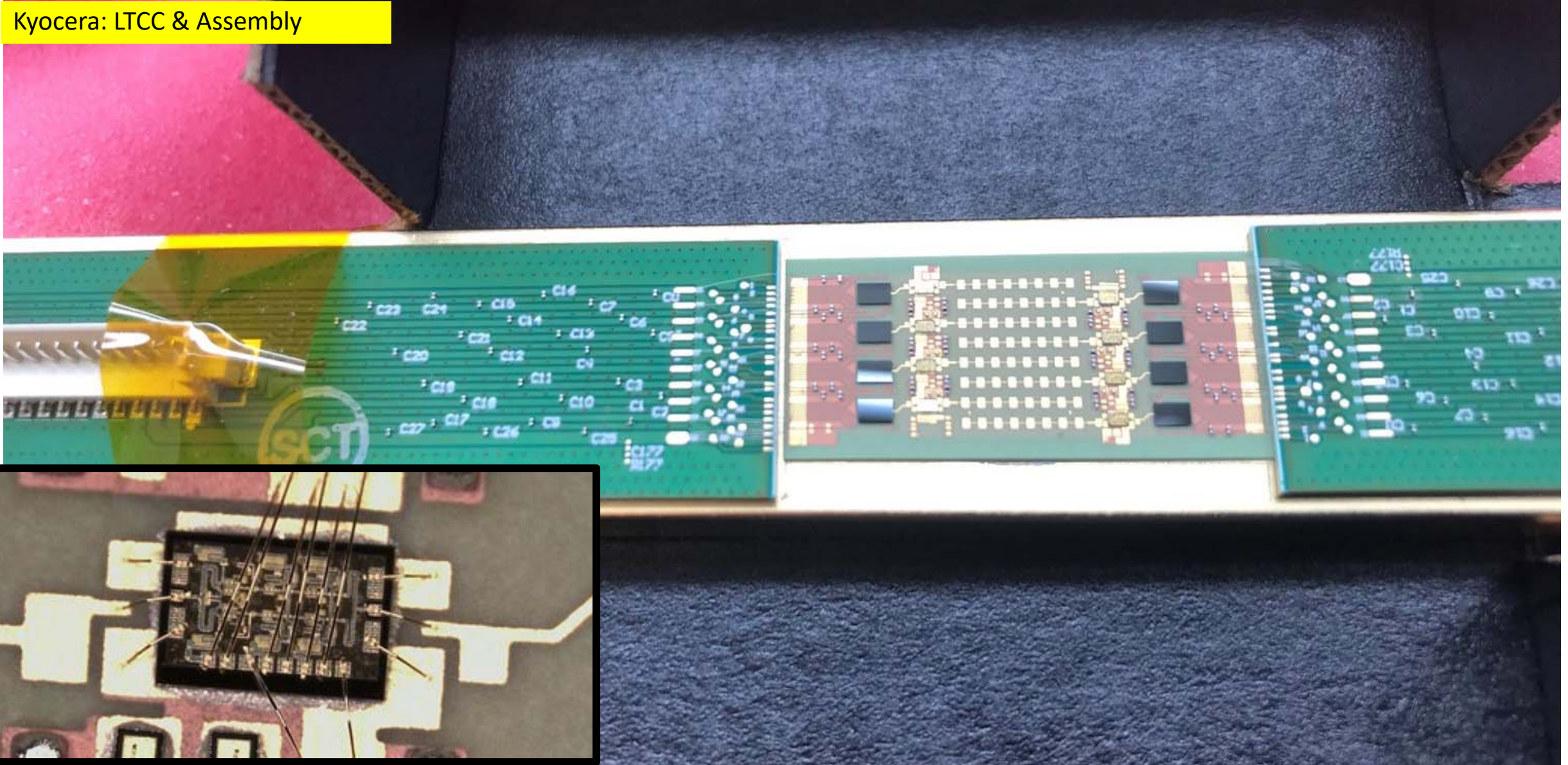
Gen-II 140GHz MIMO hub modules

Use C4 flip-chip bonds, not 50 μm Cu stud; higher yield given LTCC lithographic dimensions



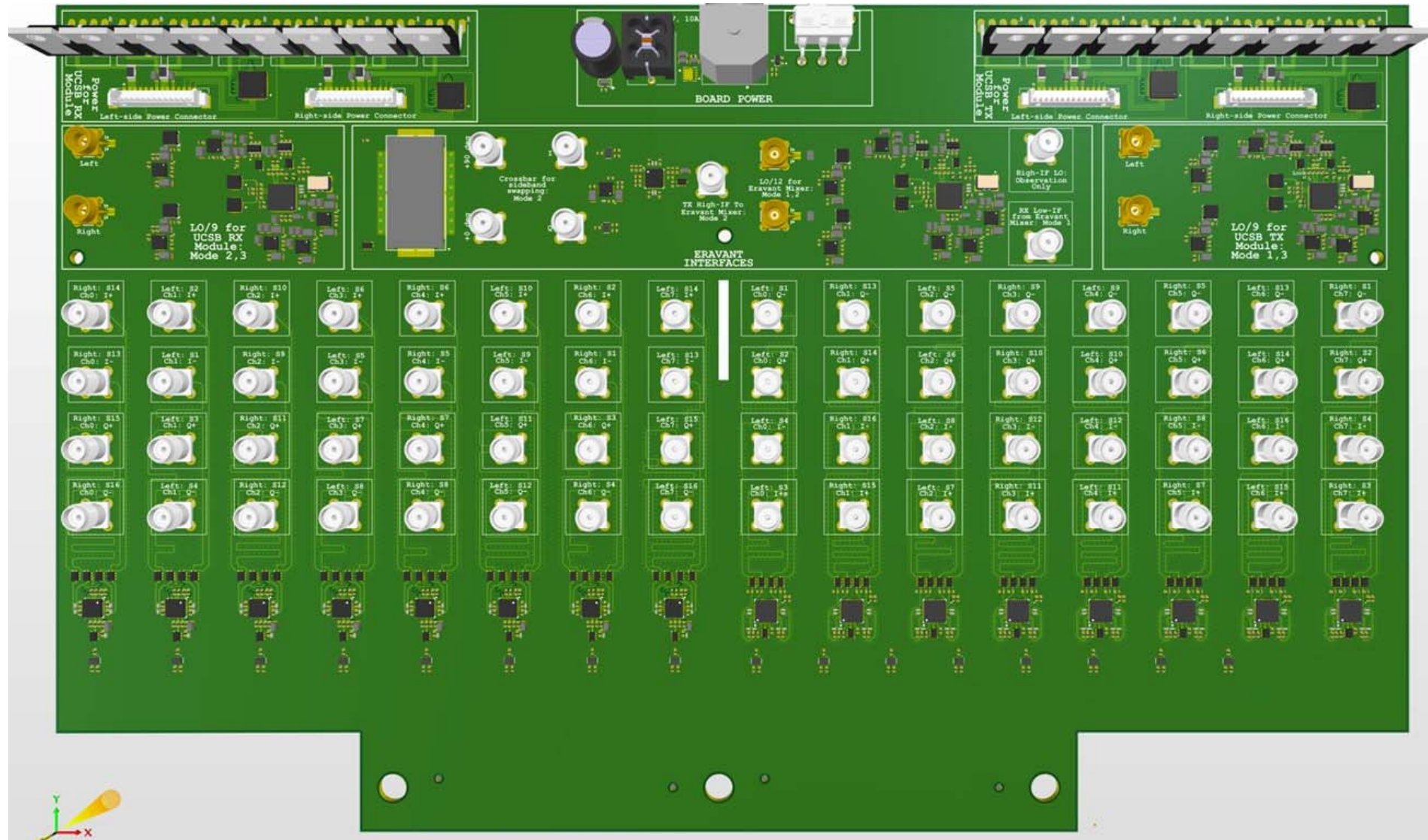
Gen-II 140GHz MIMO hub modules

Kyocera: LTCC & Assembly

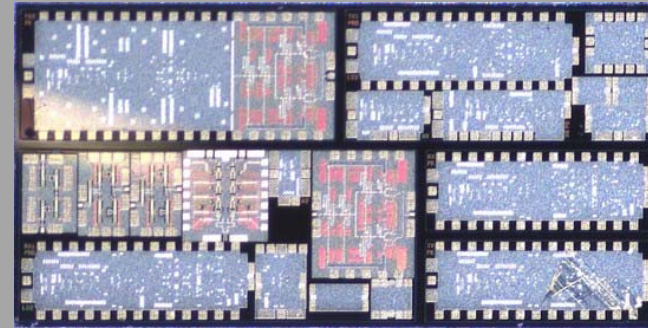
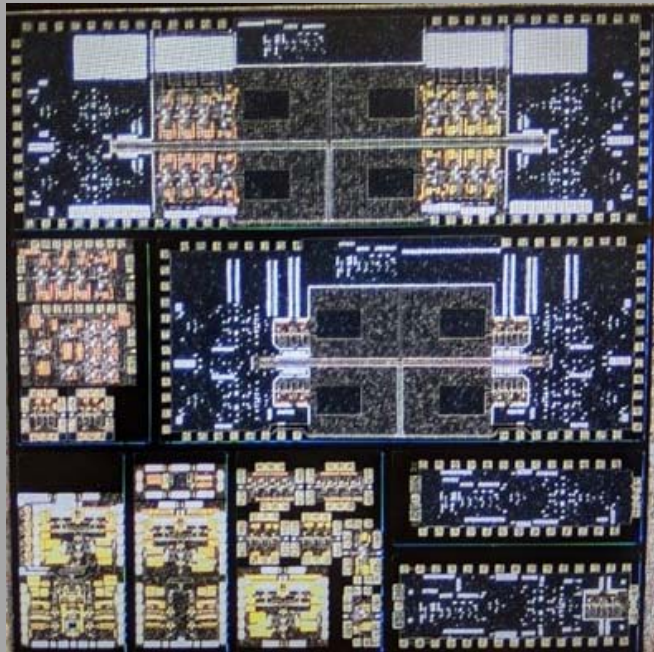


Interface PCB: 140 GHz Modules to RF-SOC PFGA

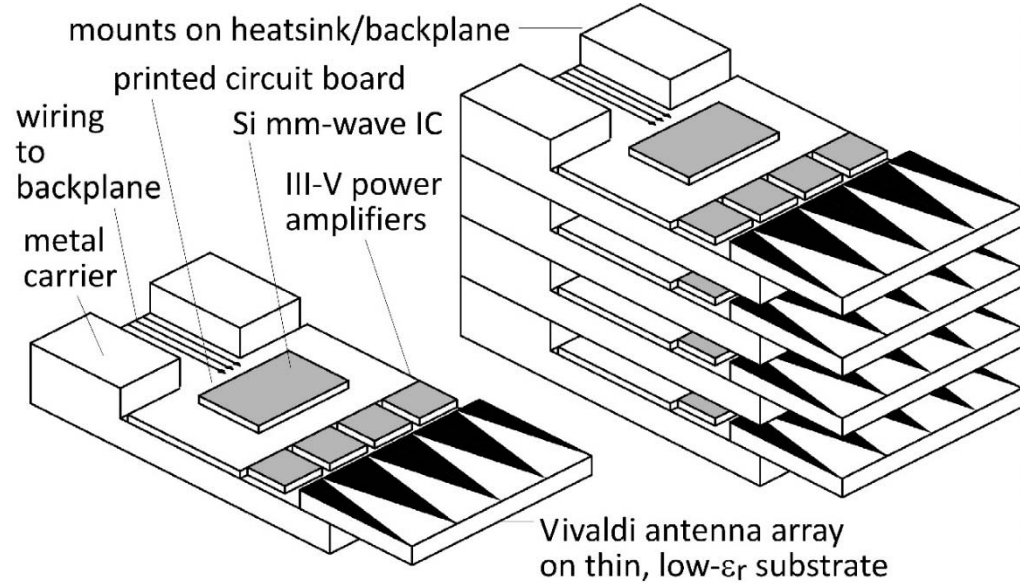
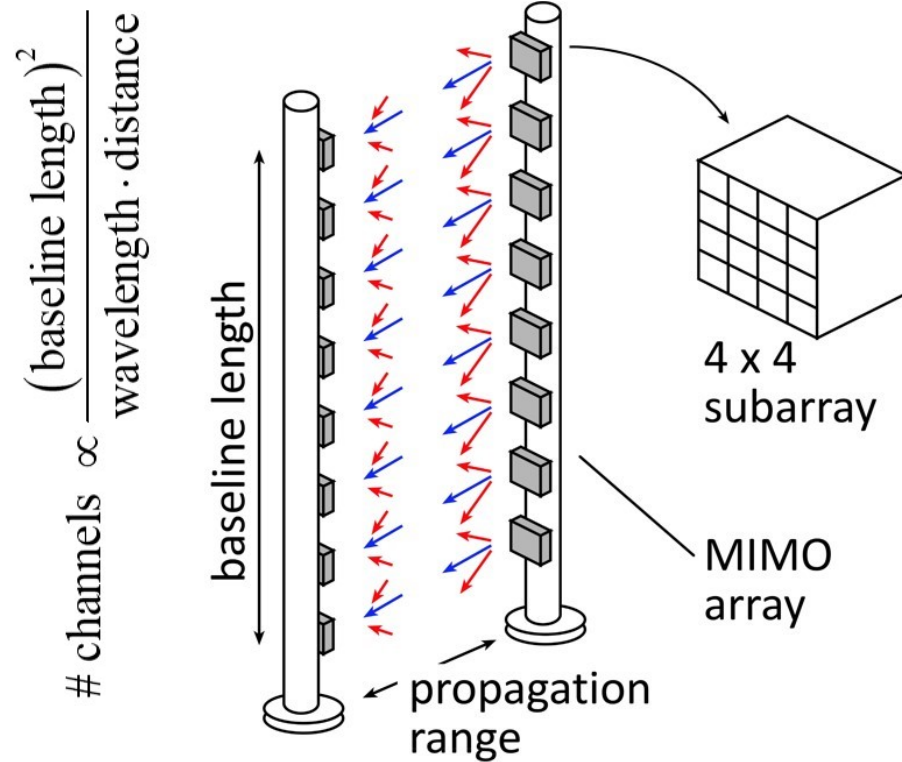
Michael Zappe, Aditya Dhananjay, Pi-Radio, Inc.



210 GHz and 280 GHz Array Modules



210 GHz, 640 Gb/s MIMO Backhaul



8-element MIMO array

2.1 m baseline.

80Gb/s/subarray → 640Gb/s total

4 × 4 sub-arrays → 8 degree beamsteering

Key link parameters

500 meters range in 50 mm/hr rain; 23 dB/km

20 dB total margins:

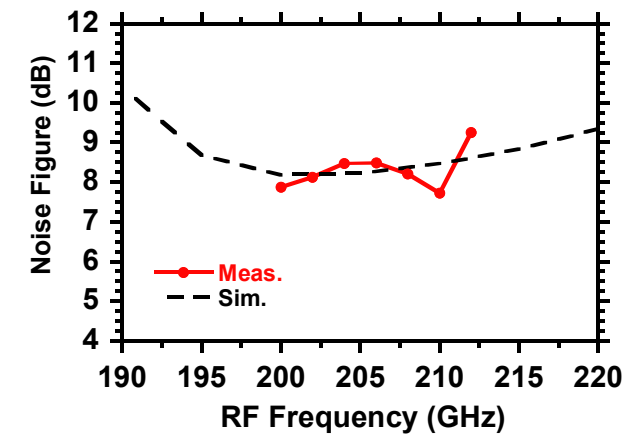
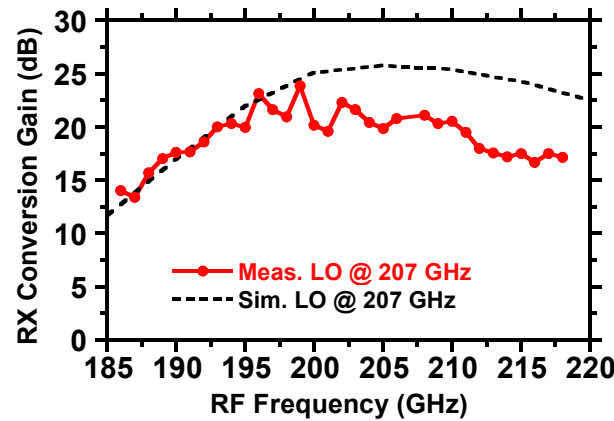
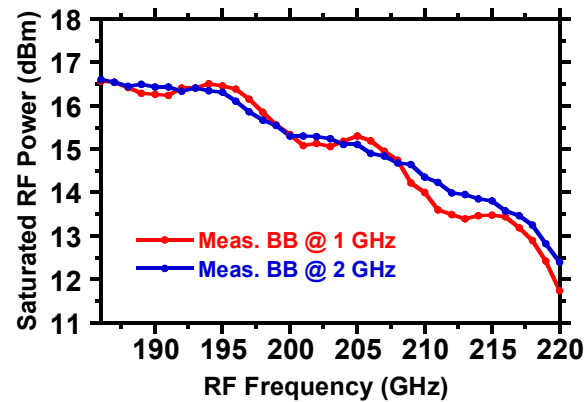
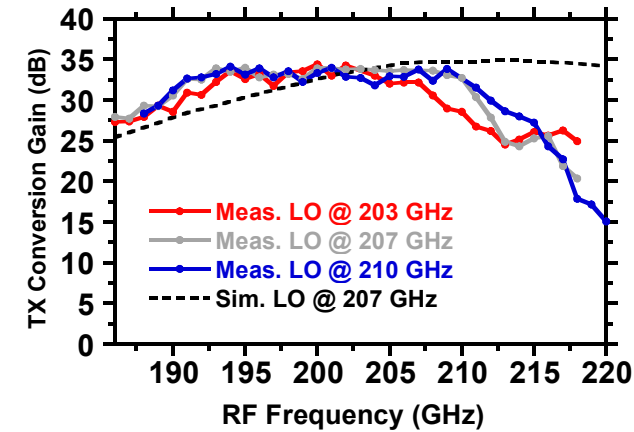
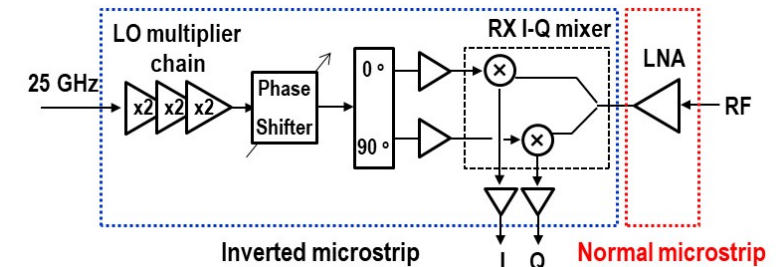
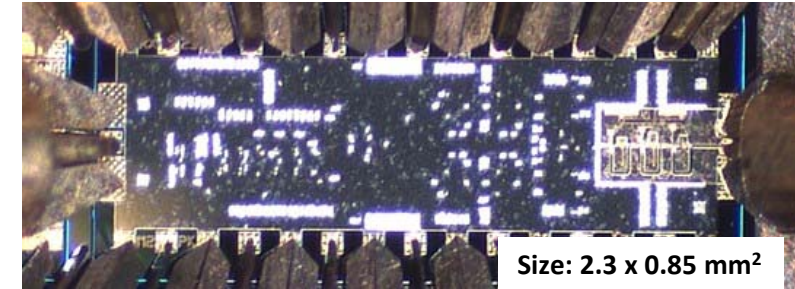
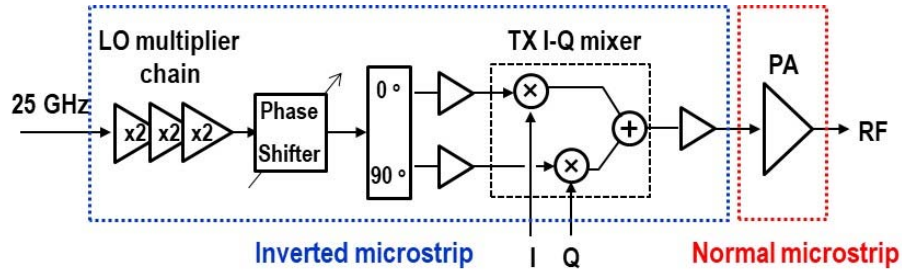
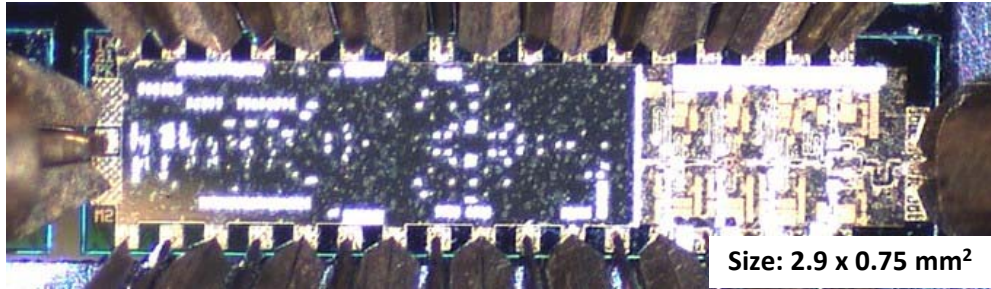
packaging loss, obstruction, operating,
design, aging

PAs: 18dBm = $P_{1\text{dB}}$ (per element)

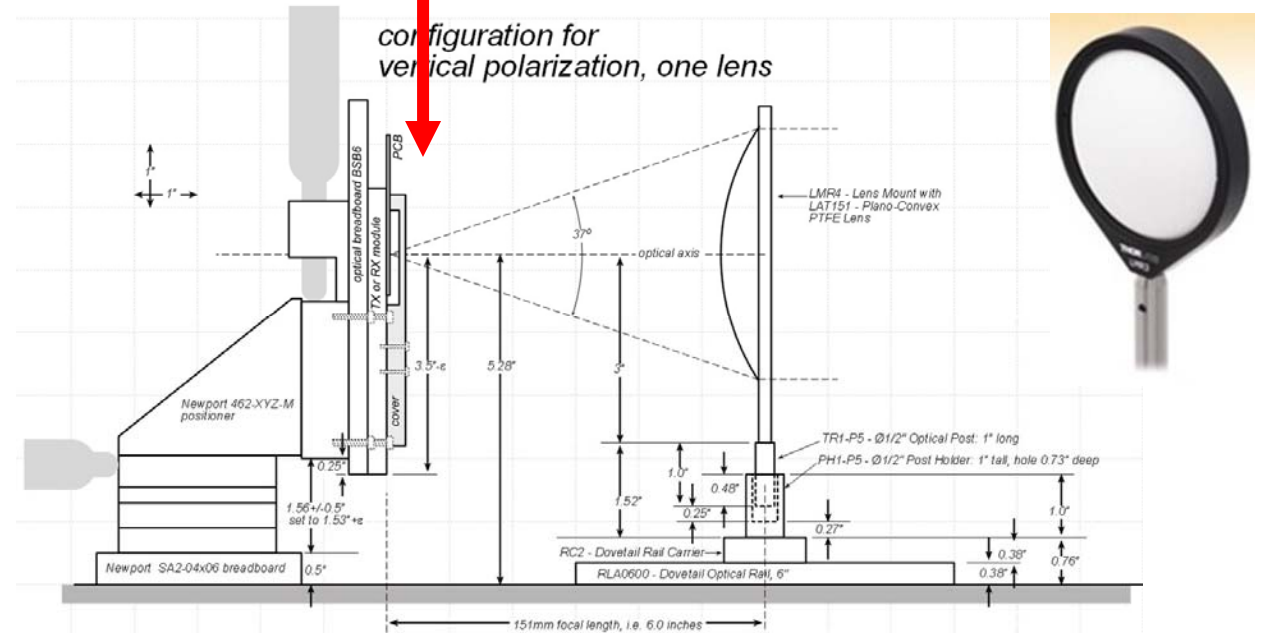
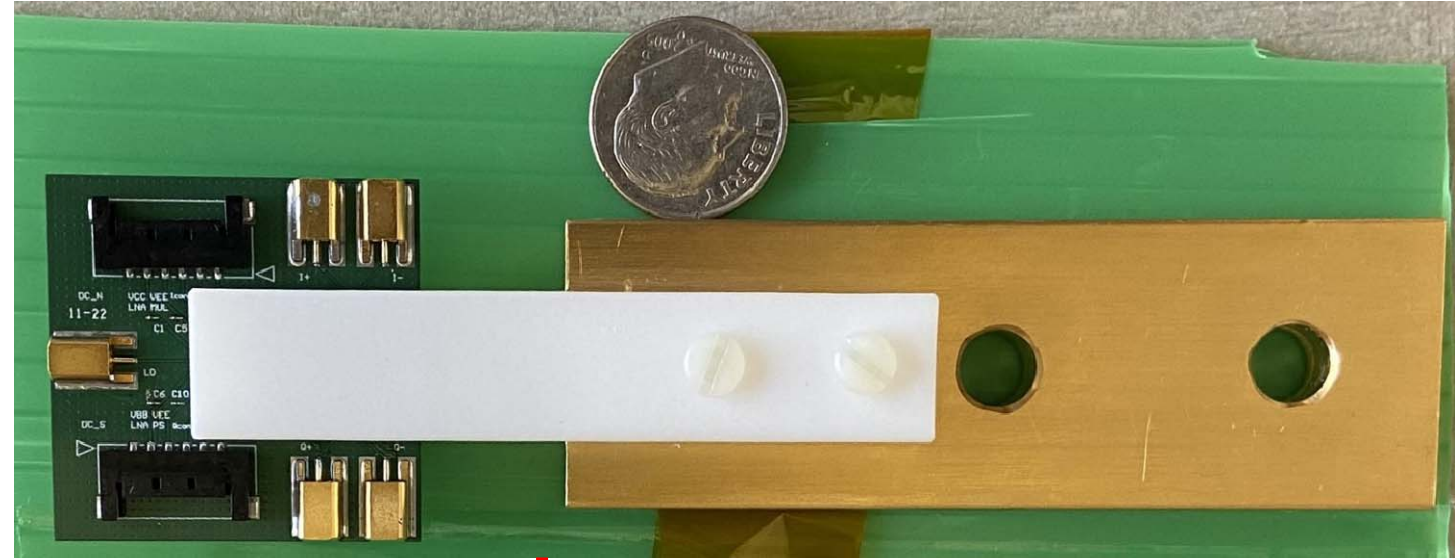
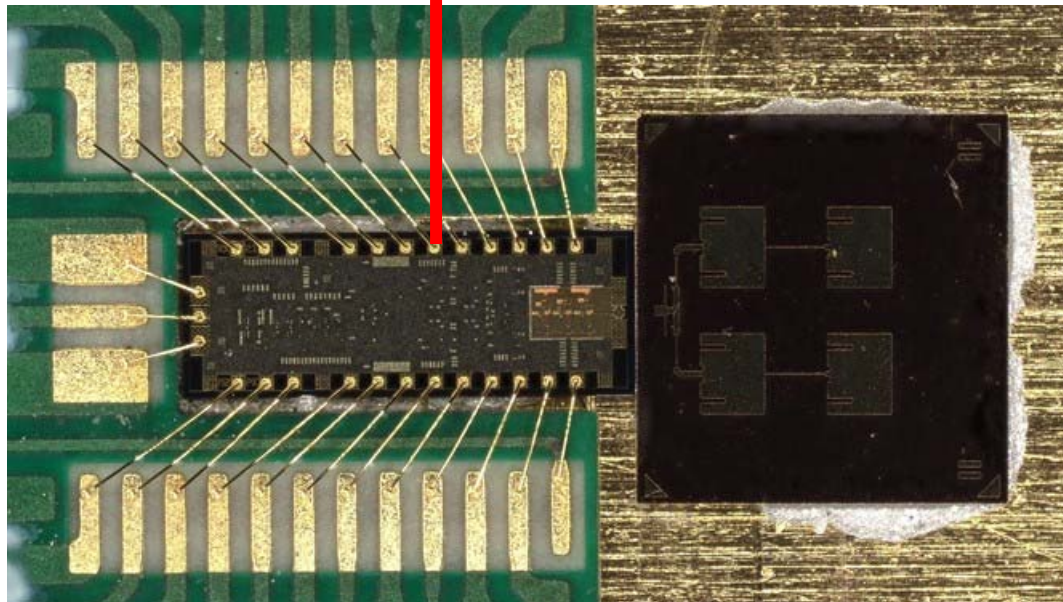
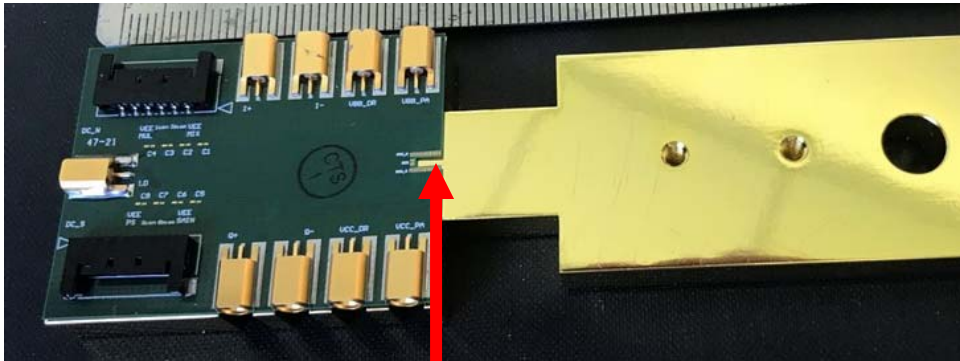
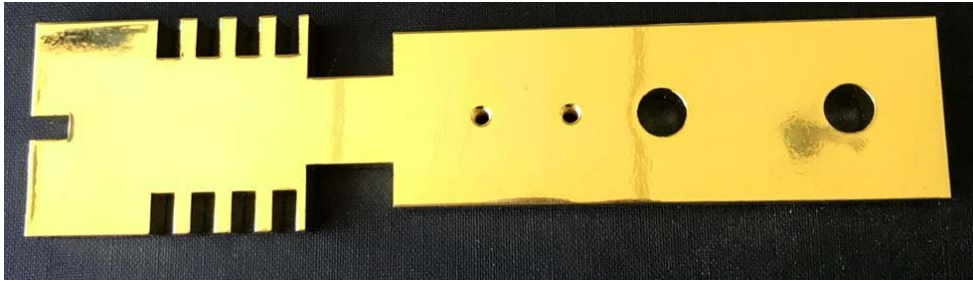
LNAs: 6dB noise figure

210 GHz Transmitter and Receiver ICs

M. Seo et al, 2021 IMS; Teledyne 250nm InP HBT

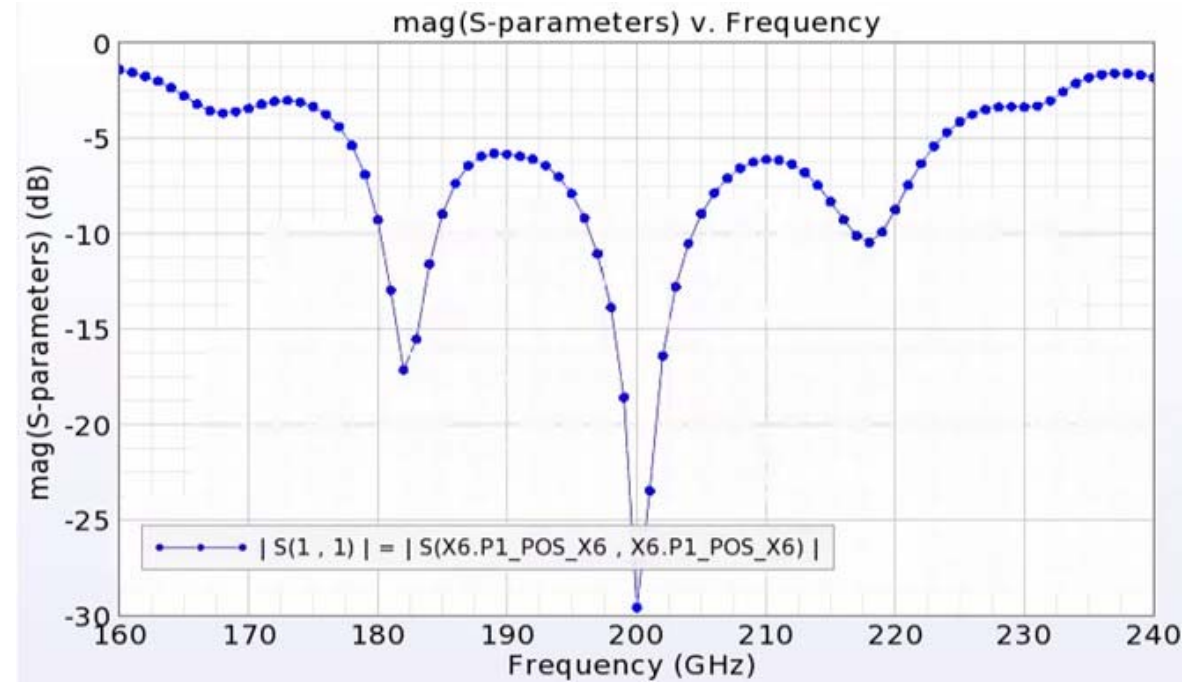
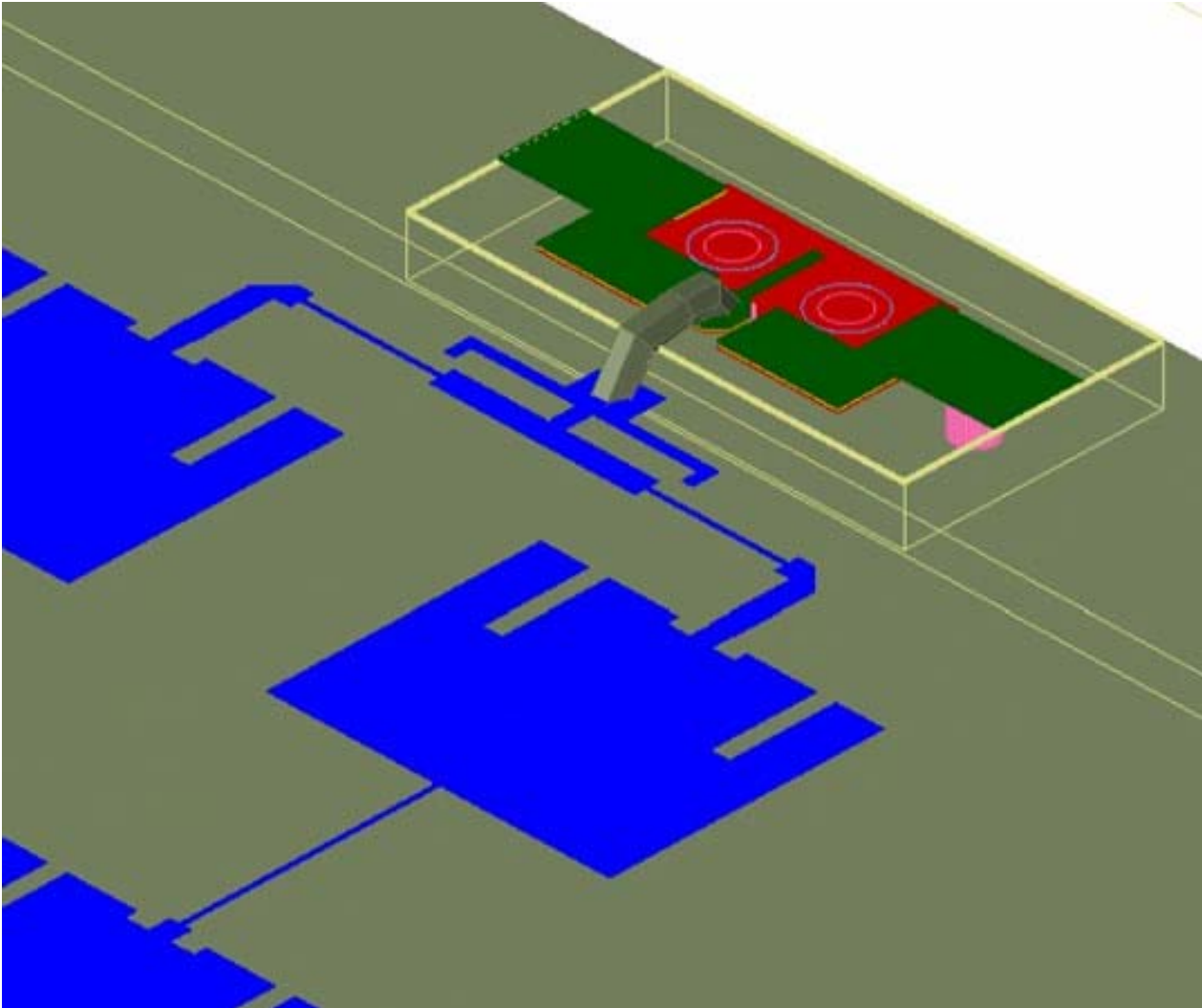


200GHz MIMO backhaul modules



200 GHz IC-Antenna Interface

20 μm spacing between pad and antenna edge



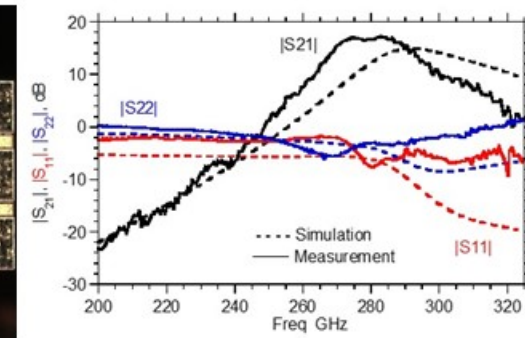
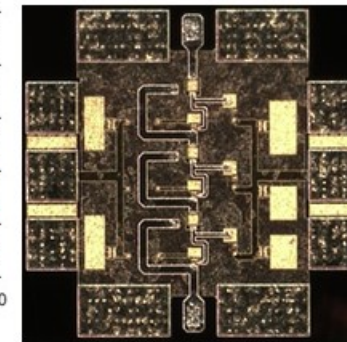
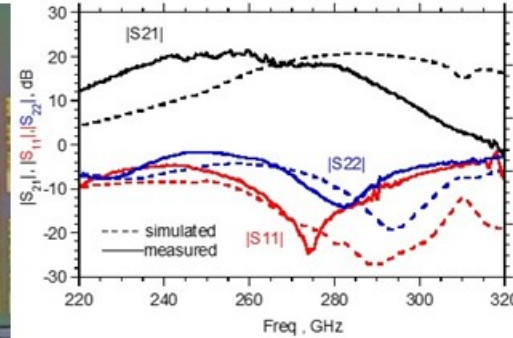
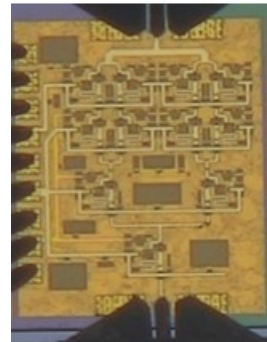
280GHz MIMO backhaul development

Amidreza, Solyu, Ahmed, Seo, UCSB

1st tapeout: PA, LNA

PA: 270 GHz, 16.7 dBm Psat, 4% PAE. ✓

LNA: 280 GHz, 15 dB gain, NF= ?? ✓



2nd tapeout: transmitter, receiver

Not all blocks yet tested

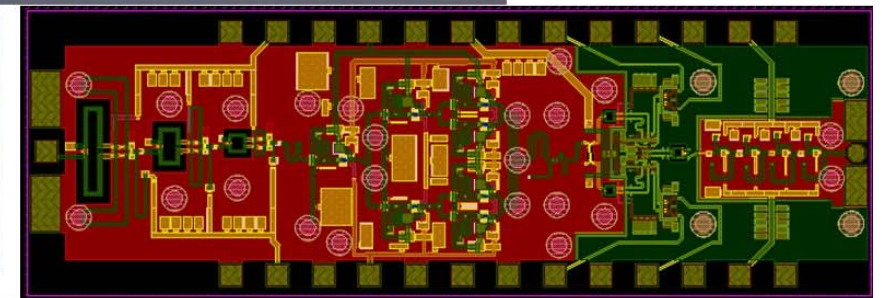
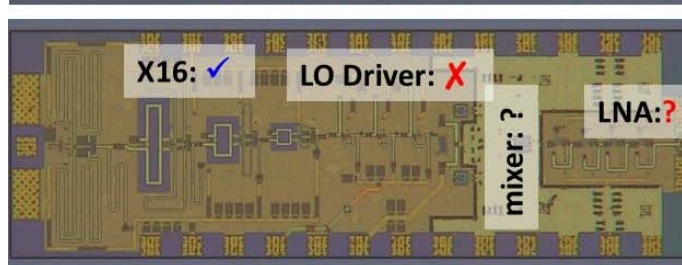
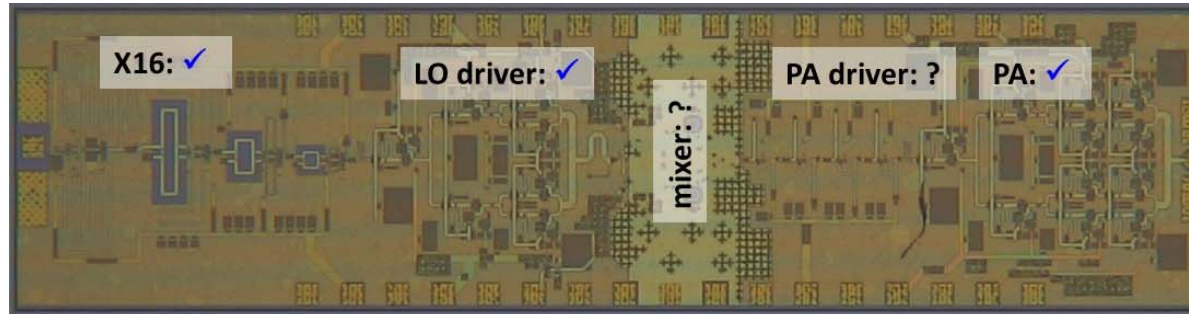
Working LO multiplier ✓

Working high-power LO driver ✓

Failed low-power LO driver ✗

Failed low-power PA driver ✗

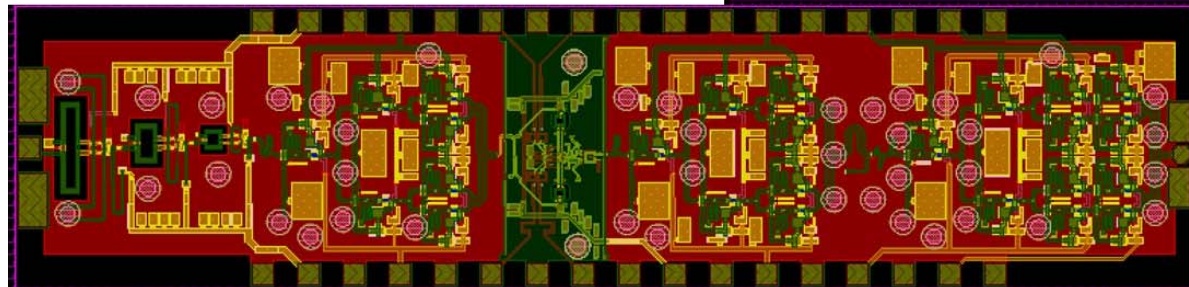
→ transmitters, receivers failed ✗



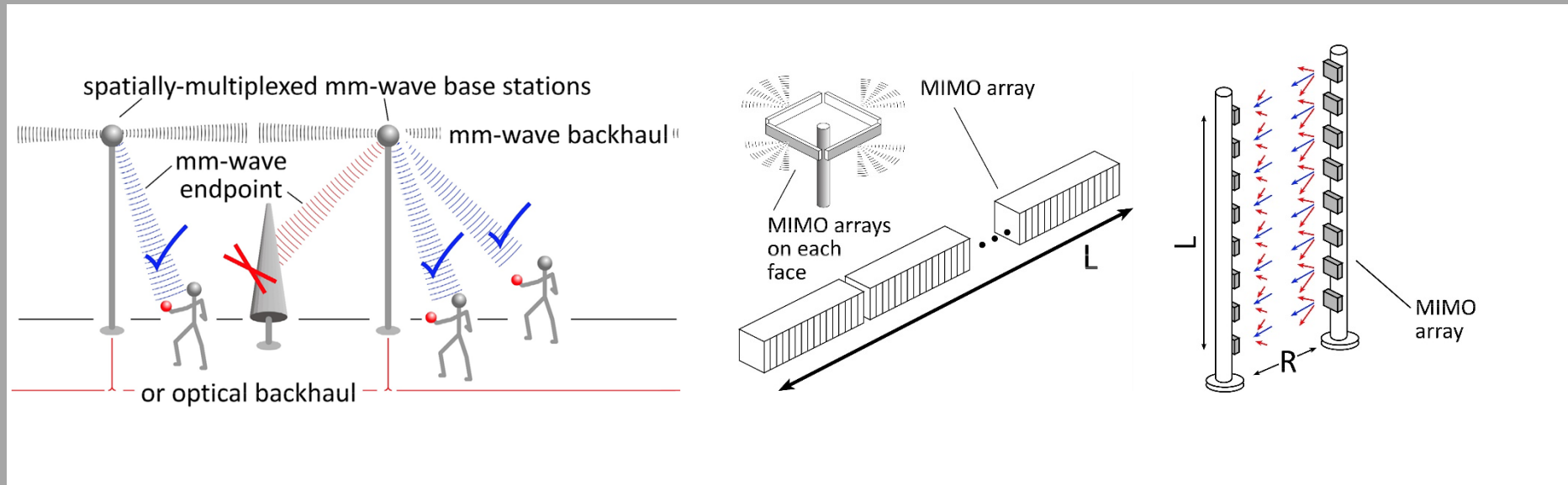
3rd tapeout: transmitter, receiver

Redesigned, LNA, LO and PA drivers

In fabrication: expected 9/2022.



100-300GHz Wireless



100-300 GHz Wireless

Massive capacities

large available bandwidths

massive spatial multiplexing in base stations and point-point links

Very short range: few 100 meters

short wavelength, high atmospheric losses. Easily-blocked beams.

IC Technology

All-silicon for short ranges below 200 GHz.

SiGe or III-V LNAs and PAs for longer-range links. Just like cell phones today

III-V frequency extenders for 340GHz and beyond

The challenges

beamformer computational complexity: looks good.

packaging: fitting signal channels in very small areas, removing the heat

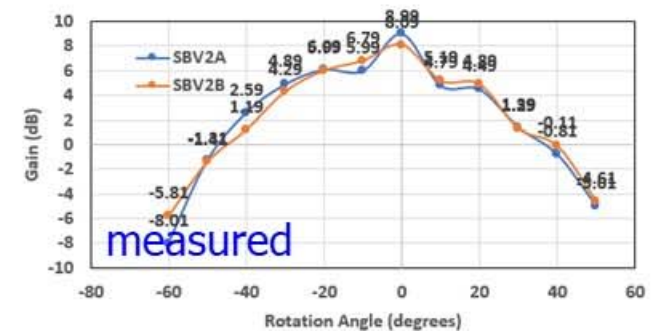
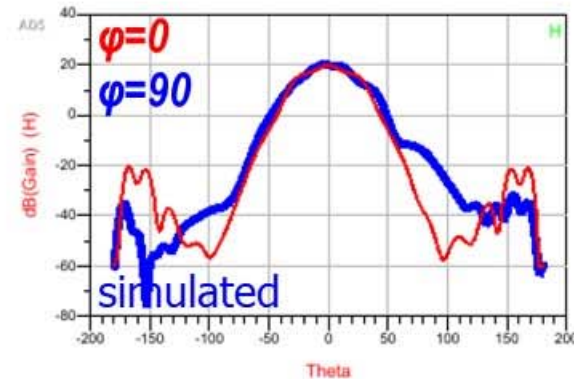
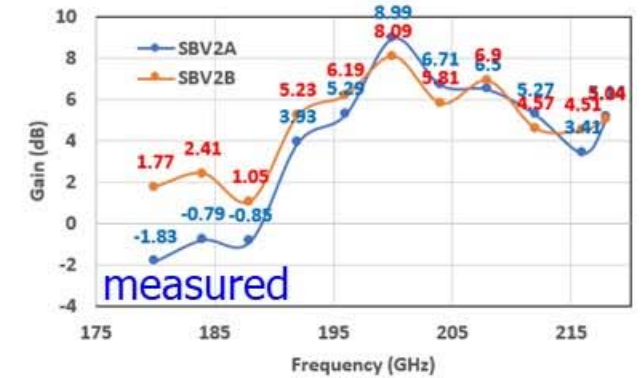
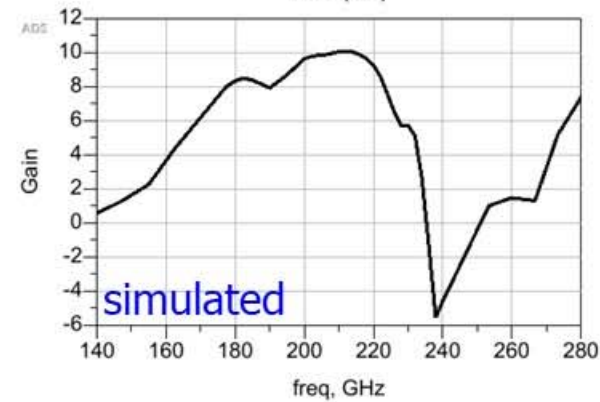
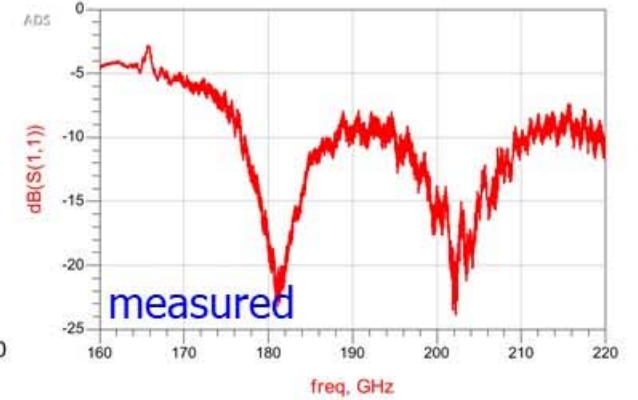
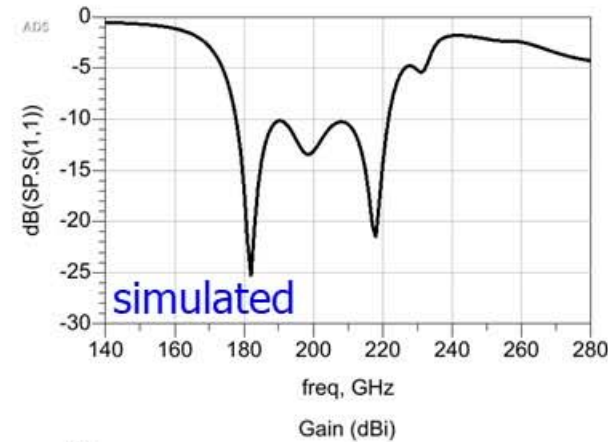
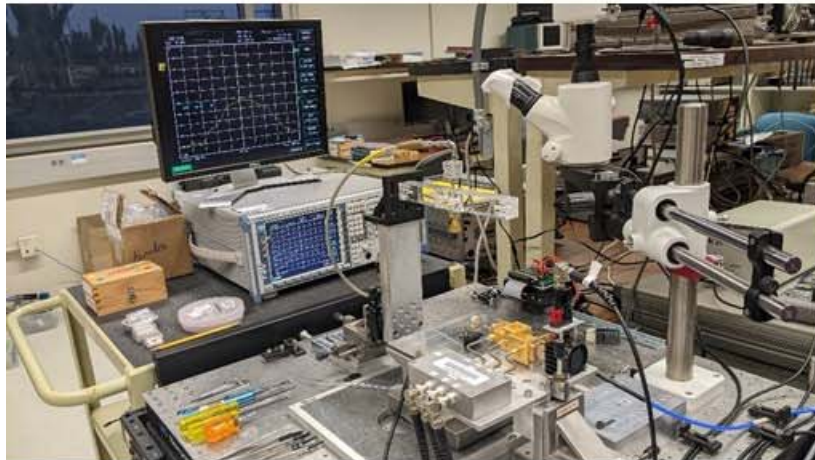
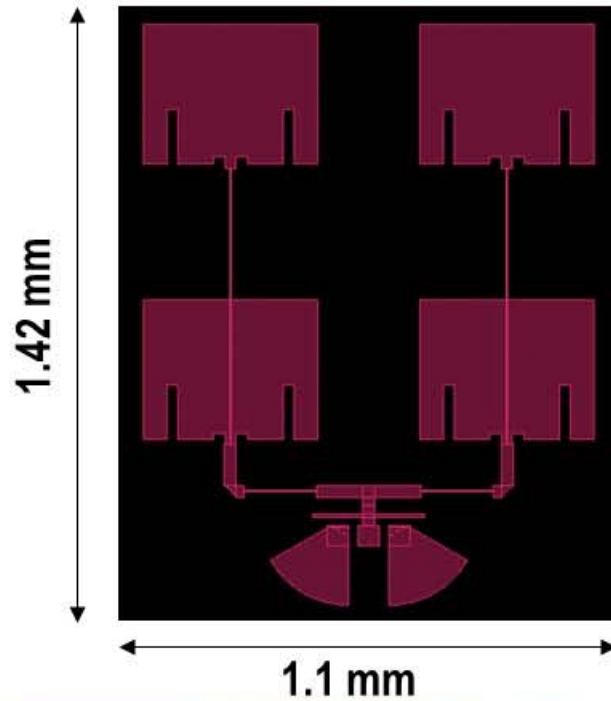
packaging: accessing advanced industry technologies in low volumes

mesh networking to accommodate beam blockage

driving the technologies to low cost

(backup files follow)

200 GHz Modules: Antennas



**In case
of questions**

70 GHz spatially multiplexed base station

If we use instead a 70GHz carrier,
the range increases to **70 meters** (vs. **40 meters**)
but the handset becomes **16mm×16mm** (vs. 8mm×8mm),
and the hub array becomes 19mm×612mm (vs. 10mm×328mm)

Or, use a 4×4 (**8mm×8mm**) handset array,
and the range becomes **..about 40 meters**.

Same handset area (more handset elements)→ same link budget
Easier to obtain license for 140±2.5GHz than 70±2.5GHz

75 GHz, 640 Gb/s MIMO backhaul (16QAM)

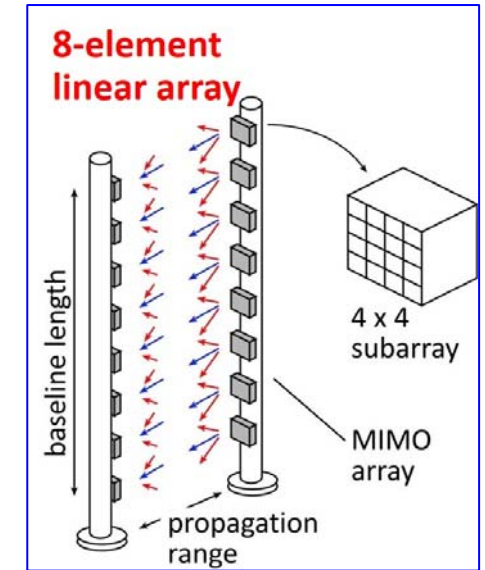
Why not use a lower-frequency carrier, e.g. 75 GHz ?

Must use at least 16QAM, given 80Gb/s/channel...

8-element 640Gb/s linear array:

requires 16dB_m transmit power/element (P_{out})

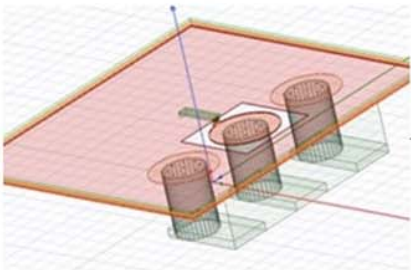
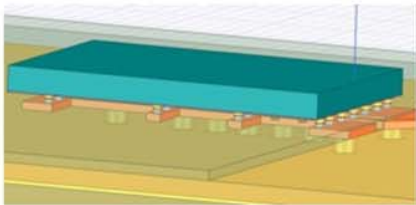
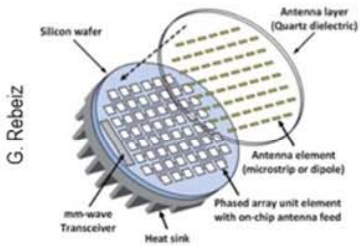
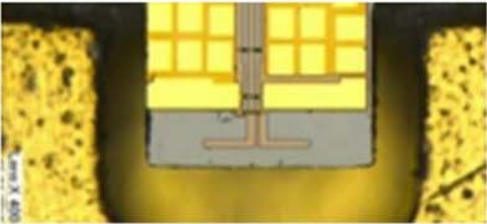
requires 3.5m linear array



Similar RF power output, physically larger

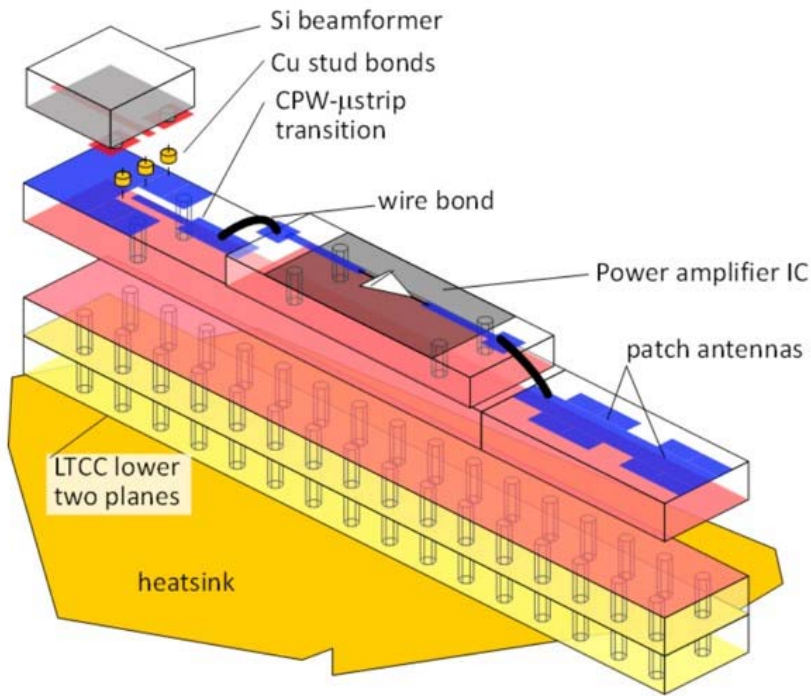
100-300GHz IC-package connections

Deal, IEEE Trans THz, Sept 2011



type	Frequency	technology	cost	heatsinking
micromachined waveguide interface	1000 GHz	Research. Cheap one day ?	high X	good
ribbon, mesh bond	200 GHz	Handcrafted.	high X	good
patch antennas on superstrate	1000 GHz	Straightforward	low	good
Cu stud flip-chip	>200 GHz	Industry standard	low	ok, marginal for PA X
hot vias	200 GHz	Development	low ?	good
(ball) wirebonds	100 GHz X	Industry standard	low	good

140GHz hub: packaging challenges



IC-package interconnects

Difficult at > 100 GHz

Removing heat

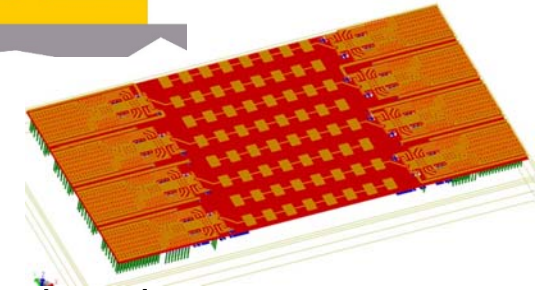
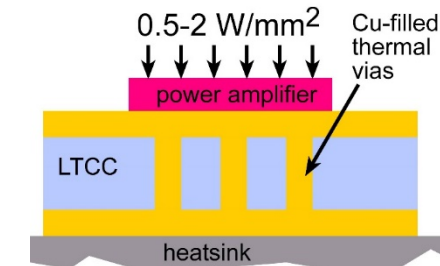
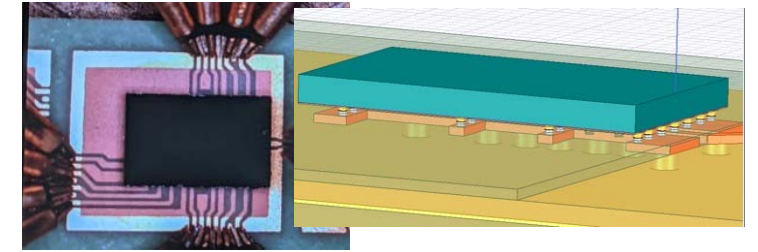
Thermal vias are marginal

Interconnect density

Dense wiring for DC, LO, IF, control.
Hard to fit these all in.

Economies of scale

Advanced packaging standards require sophisticated tools
High-volume orders only
Hard for small-volume orders (research, universities)
Packaging industry is moving offshore



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Power Amplifiers (more)

- 270GHz power amplifier: A. S. H. Ahmed, U. Soyly, M. Seo, M. Urteaga and M. J. W. Rodwell, "A compact H-band Power Amplifier with High Output Power," 2021 IEEE Radio Frequency Integrated Circuits Symposium (RFIC), 2021, pp. 123-126, doi: 10.1109/RFIC51843.2021.9490426.
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